TENTATIVE TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

64-MBIT (8M × 8 BITS) CMOS NAND E²PROM

DESCRIPTION

The TC58V64FT/DC is a single 3.3-V 64-Mbit (69,206,016-bit) NAND electrically erasable and programmable read-only memory (NAND E²PROM) organized as 528 bytes × 16 pages × 1024 blocks. The device has a 528-byte static register which allows program and read data to be transferred between the register and the memory cell array in 528-byte increments. The Erase operation is implemented in a single block unit (8 Kbytes + 256 bytes: 528 bytes × 16 pages).

The TC58V64FT/DC is a serial-type memory device which utilizes the I/O pins for both address and data input / output as well as for command inputs. The Erase and Program operations are automatically executed making the device most suitable for applications such as solid-state file storage, voice recording, image file memory for still cameras and other systems which require high-density non-volatile memory data storage.

FEATURES

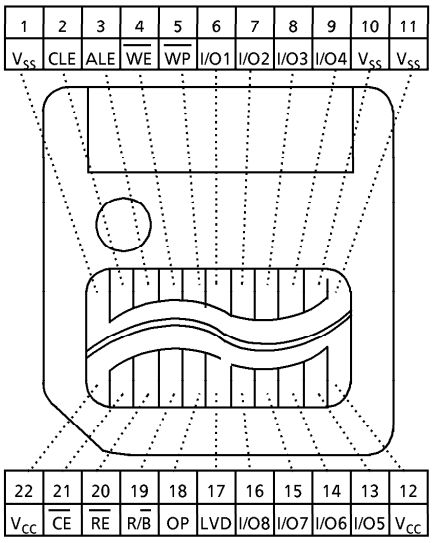
- Organization
  - Memory cell array 528 × 16K × 8
  - Register 528 × 8
  - Page size 528 bytes
  - Block size (8K + 256) bytes
- Modes
  - Read, Reset, Auto Page Program
  - Auto Block Erase, Status Read
- Mode control
  - Serial input/output
  - Command control
- Power supply
  - V_{CC} = 3.3 V ± 0.3 V
- Access time
  - Cell array-register 7 μs max
  - Serial Read cycle 50 ns min
- Operating current
  - Read (50-ns cycle) 10 mA typ.
  - Program (avg.) 10 mA typ.
  - Erase (avg.) 10 mA typ.
  - Standby 100 μA
- Packages
  - TC58V64FT: TSOP II 44/40 - P - 400 - 0.80B (Weight: 0.48 g typ.)
  - TC58V64DC: FDC - 22A (Weight: 1.8 g typ.)

PIN ASSIGNMENT (TOP VIEW)

TC58V64FT

V_{SS}	1	44	V_{CC}
CLE	2	43	$\overline{CE}$
ALE	3	42	$\overline{RE}$
$\overline{WE}$	4	41	R/$\overline{B}$
$\overline{WP}$	5	40	OP
NC	6	39	NC
NC	7	38	NC
NC	8	37	NC
NC	9	36	NC
NC	10	35	NC
	11	34	
	12	33	
NC	13	32	NC
NC	14	31	NC
NC	15	30	NC
NC	16	29	NC
NC	17	28	NC
I/O1	18	27	I/O8
I/O2	19	26	I/O7
I/O3	20	25	I/O6
I/O4	21	24	I/O5
V_{SS}	22	23	V_{CC}Q

TC58V64DC



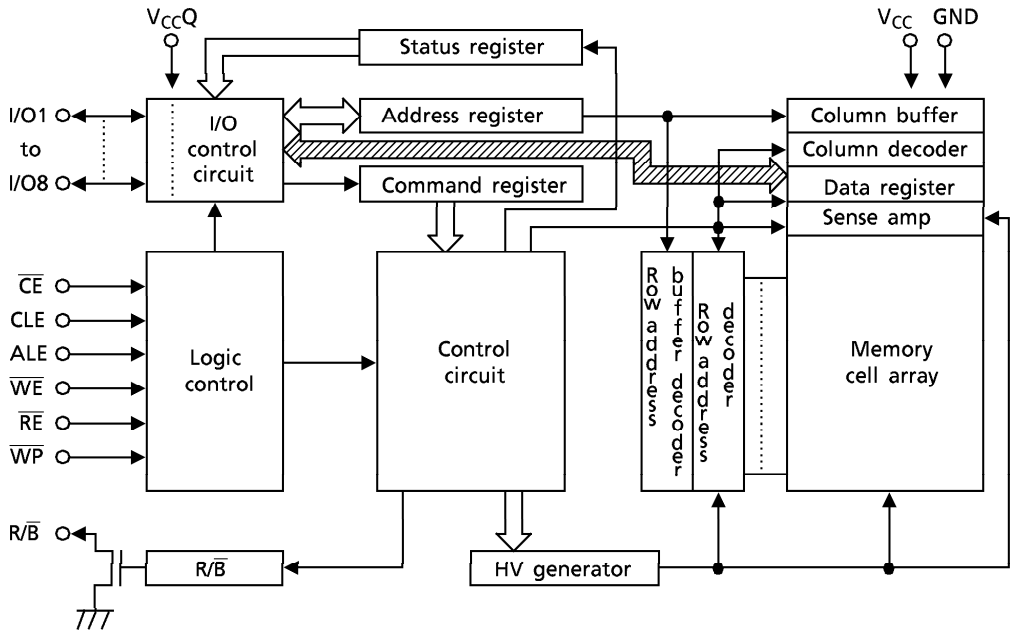
PIN NAMES

I/O1 to 8	I/O Port
$\overline{CE}$	Chip Enable
$\overline{WE}$	Write Enable
$\overline{RE}$	Read Enable
CLE	Command Latch Enable
ALE	Address Latch Enable
$\overline{WP}$	Write Protect
R/$\overline{B}$	Ready/Busy
OP	Option Pin
LVD	Low Voltage Detect
V_{CC}	Power Supply
V_{CC}Q	Output Buffer Power Supply
V_{SS}	Ground

OP: GND Input: 528 Bytes/page operation
V_{CC} Input: 512 Bytes/page operation

961001EBA1

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

SYMBOL	ITEM	RATING		UNIT
		TC58V64FT	TC58V64DC	
V_{CC}	Power Supply Voltage	-0.6 to 4.6	-0.6 to 4.6	V
$V_{CC}Q$	Output Buffer Power Supply Voltage	-0.6 to 6.0	–	V
V_{IN}	Input Voltage	-0.6 to 6.0	-0.6 to 4.6	V
$V_{I/O}$	Input / Output Voltage	-0.6 V ~ $V_{cc}Q$ + 0.3 V(≦6.0 V)	-0.6 V ~ V_{cc} + 0.3 V(≦4.6 V)	V
P_D	Power Dissipation	0.3	0.3	W
T_{SOLDER}	Soldering Temperature (10 s)	260	–	°C
T_{STG}	Storage Temperature	-55 to 150	-20 to 65	°C
T_{OPR}	Operating Temperature	0 to 70	0 to 55	°C

CAPACITANCE *(Ta = 25°C, f = 1 MHz)

SYMBOL	PARAMETER	CONDITION	MIN	TYP.	MAX	UNIT
C_{IN}	Input	V_{IN} = 0 V	–	5	10	pF
C_{OUT}	Output	V_{OUT} = 0 V	–	5	10	pF

* This parameter is periodically sampled and is not tested for every device.

VALID BLOCKS (1)

SYMBOL	PARAMETER	TC58V64FT/DC			UNIT
		MIN	TYP.	MAX	
N_{VB}	Number of Valid Blocks	1014	1020	1024	Blocks

(1) The TC58V64FT/DC occasionally contains unusable blocks. Refer to Application Note 13 toward the end of this document.

RECOMMENDED DC OPERATING CONDITIONS

SYMBOL	PARAMETER	TC58V64FT			TC58V64DC			UNIT
		MIN	TYP.	MAX	MIN	TYP.	MAX	
V_{CC}	Power Supply Voltage	3.0	3.3	3.6	3.0	3.3	3.6	V
$V_{CC}q$	Output Buffer Power Supply Voltage	3.0	–	5.5	–	–	–	V
V_{IH}	High Level Input Voltage	2.0	–	$V_{CC}Q + 0.3$	2.0	–	$V_{CC} + 0.3$	V
V_{IL}	Low Level Input Voltage	-0.3*	–	0.8	-0.3*	–	0.8	V

* –2 V (pulse width ≦ 20 ns)

DC CHARACTERISTICS

(TC58V64FT: Ta = 0° to 70°C, V_{CC} = 3.3 V ± 0.3 V, $V_{CC}Q$ = 3.0 V to 5.5 V)
(TC58V64DC: Ta = 0° to 55 °C, V_{CC} = 3.3 V ± 0.3 V)

SYMBOL	PARAMETER	CONDITION	MIN	TYP.	MAX	UNIT
I_{IL}	Input Leakage Current	V_{IN} = 0 V to $V_{CC}Q$	–	–	± 10	μA
I_{LO}	Output Leakage Current	V_{OUT} = 0.4 V to $V_{CC}Q$	–	–	± 10	μA
I_{CCO1}	Operating Current (Serial Read)	$\overline{CE}$ = V_{IL}, I_{OUT} = 0 mA, t_{cycle} = 50 ns	–	10	30	mA
I_{CCO3}	Operating Current (Command Input)	t_{cycle} = 50 ns	–	10	30	mA
I_{CCO4}	Operating Current (Data Input)	t_{cycle} = 50 ns	–	10	30	mA
I_{CCO5}	Operating Current (Address Input)	t_{cycle} = 50 ns	–	10	30	mA
I_{CCO7}	Programming Current	–	–	10	30	mA
I_{CCO8}	Erasing Current	–	–	10	30	mA
I_{CCS1}	Standby Current	$\overline{CE}$ = V_{IH}	–	–	1	mA
I_{CCS2}	Standby Current	$\overline{CE}$ = $V_{CC}Q$ – 0.2 V	–	–	100	μA
V_{OH}	High Level Output Voltage	I_{OH} = -400 μA	2.4	–	–	V
V_{OL}	Low Level Output Voltage	I_{OL} = 2.1 mA	–	–	0.4	V
$I_{OL}(R/\overline{B})$	Output Current of R/$\overline{B}$ Pin	V_{OL} = 0.4 V	–	8	–	mA

AC CHARACTERISTICS AND RECOMMENDED OPERATING CONDITIONS

(TC58V64FT: Ta = 0° to 70°C, V_{CC} = 3.3 V ± 0.3 V, $V_{CC}Q$ = 3.0 V to 5.5 V)
(TC58V64DC: Ta = 0° to 55 °C, V_{CC} = 3.3 V ± 0.3 V)

SYMBOL	PARAMETER	MIN	MAX	UNIT	NOTES
t_{CLS}	CLE Setup Time	0	–	ns	
t_{CLH}	CLE Hold Time	10	–	ns	
t_{CS}	$\overline{CE}$ Setup Time	0	–	ns	
t_{CH}	$\overline{CE}$ Hold Time	10	–	ns	
t_{WP}	Write Pulse Width	25	–	ns	
t_{ALS}	ALE Setup Time	0	–	ns	
t_{ALH}	ALE Hold Time	10	–	ns	
t_{DS}	Data Setup Time	20	–	ns	
t_{DH}	Data Hold Time	10	–	ns	
t_{WC}	Write Cycle Time	50	–	ns	
t_{WH}	$\overline{WE}$-High Hold Time	15	–	ns	
t_{WW}	$\overline{WP}$ High to $\overline{WE}$ Low	100	–	ns	
t_{RR}	Ready-to-$\overline{RE}$ Falling Edge	20	–	ns	
t_{RP}	Read Pulse Width	35	–	ns	
t_{RC}	Read Cycle Time	50	–	ns	
t_{REA}	$\overline{RE}$ Access Time (Serial Data Access)	–	35	ns	
t_{CEH}	$\overline{CE}$-High Time for Last Address in Serial Read Cycle	100	–	ns	(3)
t_{REAID}	$\overline{RE}$ Access Time (ID Read)	–	35	ns	
t_{OH}	Data Output Hold Time	10	–	ns	
t_{RHZ}	$\overline{RE}$-High-to-Output-High Impedance	–	30	ns	
t_{CHZ}	$\overline{CE}$-High-to-Output-High Impedance	–	20	ns	
t_{REH}	$\overline{RE}$-High Hold Time	15	–	ns	
t_{IR}	Output-High-Impedance-to-$\overline{RE}$ Rising Edge	0	–	ns	
t_{RSTO}	$\overline{RE}$ Access Time (Status Read)	–	35	ns	
t_{CSTO}	$\overline{CE}$ Access Time (Status Read)	–	45	ns	
t_{RHW}	$\overline{RE}$ High to $\overline{WE}$ Low	0	–	ns	
t_{WHC}	$\overline{WE}$ High to $\overline{CE}$ Low	30	–	ns	
t_{WHR}	$\overline{WE}$ High to $\overline{RE}$ Low	30	–	ns	
t_{AR1}	ALE Low to $\overline{RE}$ Low (ID Read)	100	–	ns	
t_{CR}	$\overline{CE}$ Low to $\overline{RE}$ Low (ID Read)	100	–	ns	
t_R	Memory Cell Array to Starting Address	–	7	μs	
t_{WB}	$\overline{WE}$ High to Busy	–	100	ns	
t_{AR2}	ALE Low to $\overline{RE}$ Low (Read Cycle)	50	–	ns	
t_{RB}	$\overline{RE}$ Last Clock Rising Edge to Busy (in Sequential Read)	–	100	ns	
t_{CRY}	$\overline{CE}$ High to Ready (When interrupted by $\overline{CE}$ in Read Mode)	–	50 + tr (R/$\overline{B}$)	ns	(2)
t_{RST}	Device Reset Time (Read/Program/Erase)	–	6/10/500	μs	

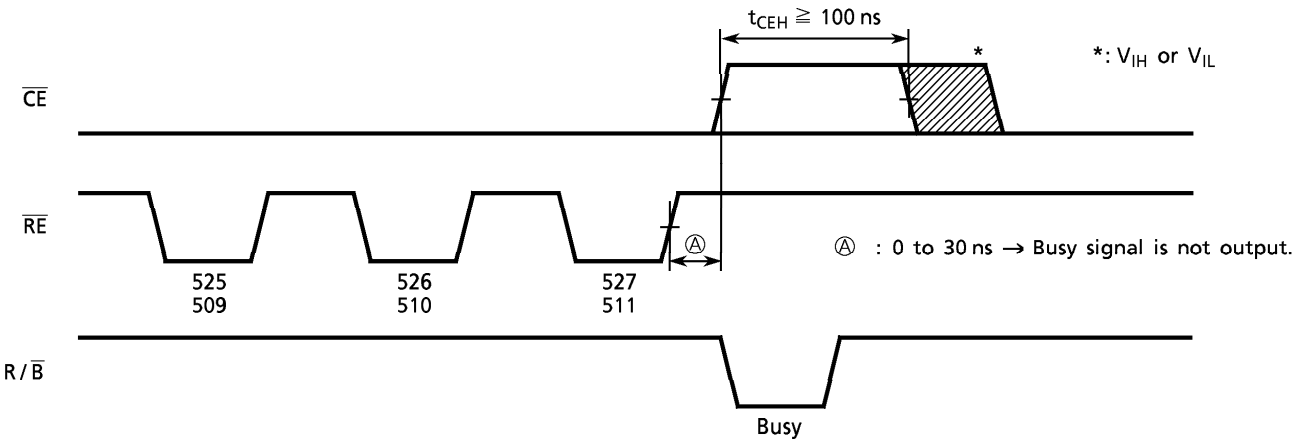
AC TEST CONDITIONS

Input level	:	2.4 V / 0.4 V
Input comparison level	:	1.5 V / 1.5 V
Output data comparison level	:	1.5 V / 1.5 V
Output load	:	1 TTL + C_L (100 pF)

(1) Transition time (t_T) = 5 ns

(2) $\overline{CE}$-High-to-Ready time depends on the pull-up resistor tied to the R/$\overline{B}$ pin. (Refer to Application Note 10 toward the end of this document.)

(3) If the delay between $\overline{RE}$ and $\overline{CE}$ is less than 200 ns and t_{CEH} is greater than or equal to 100 ns, reading will stop.
If the $\overline{RE}$-to-$\overline{CE}$ delay is less than 30 ns, the device will not re-enter Busy state.



PROGRAMMING AND ERASING CHARACTERISTICS

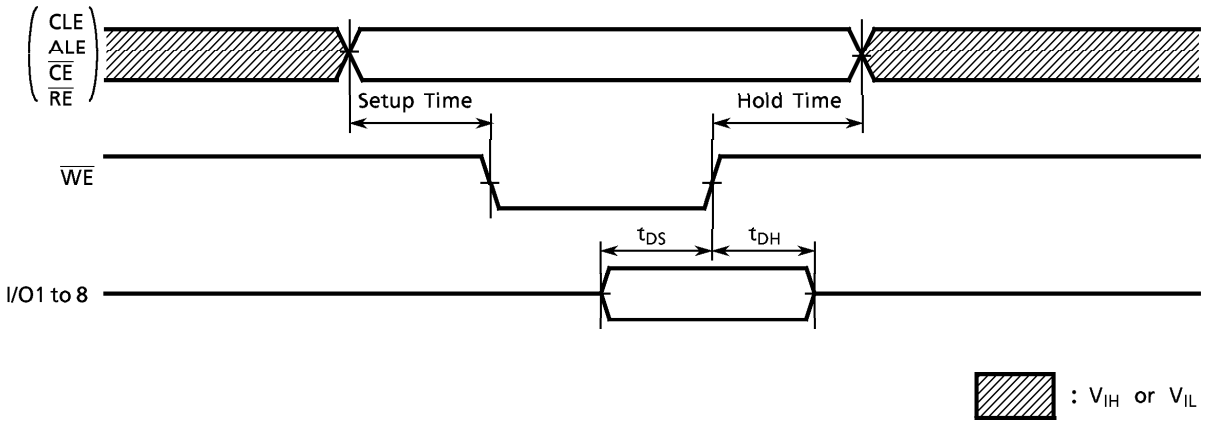
(TC58V64FT: Ta = 0° to 70 °C, V_{CC} = 3.3 V ± 0.3 V, $V_{CC}Q$ = 3.0 V to 5.5 V)
(TC58V64DC: Ta = 0° to 55 °C, V_{CC} = 3.3 V ± 0.3 V)

SYMBOL	PARAMETER	MIN	TYP.	MAX	UNIT	NOTES
t_{PROG}	Average Programming Time		200	1000	μs	
N	Number of Programming Cycles on Same Page			10		(1)
t_{BERASE}	Block Erasing Time		2	20	ms	
P/E	Number of Program/Erase Cycles			1×10^6		(2)

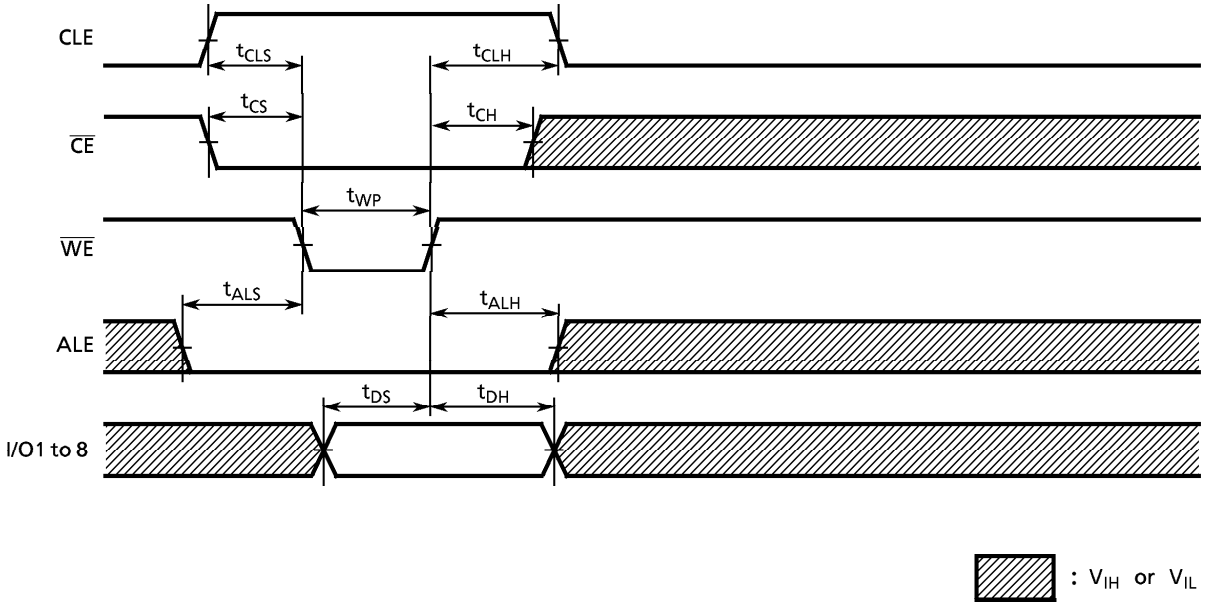
(1) Refer to Application Note 11 toward the end of this document.
(2) Refer to Application Note 14 toward the end of this document.

TIMING DIAGRAMS

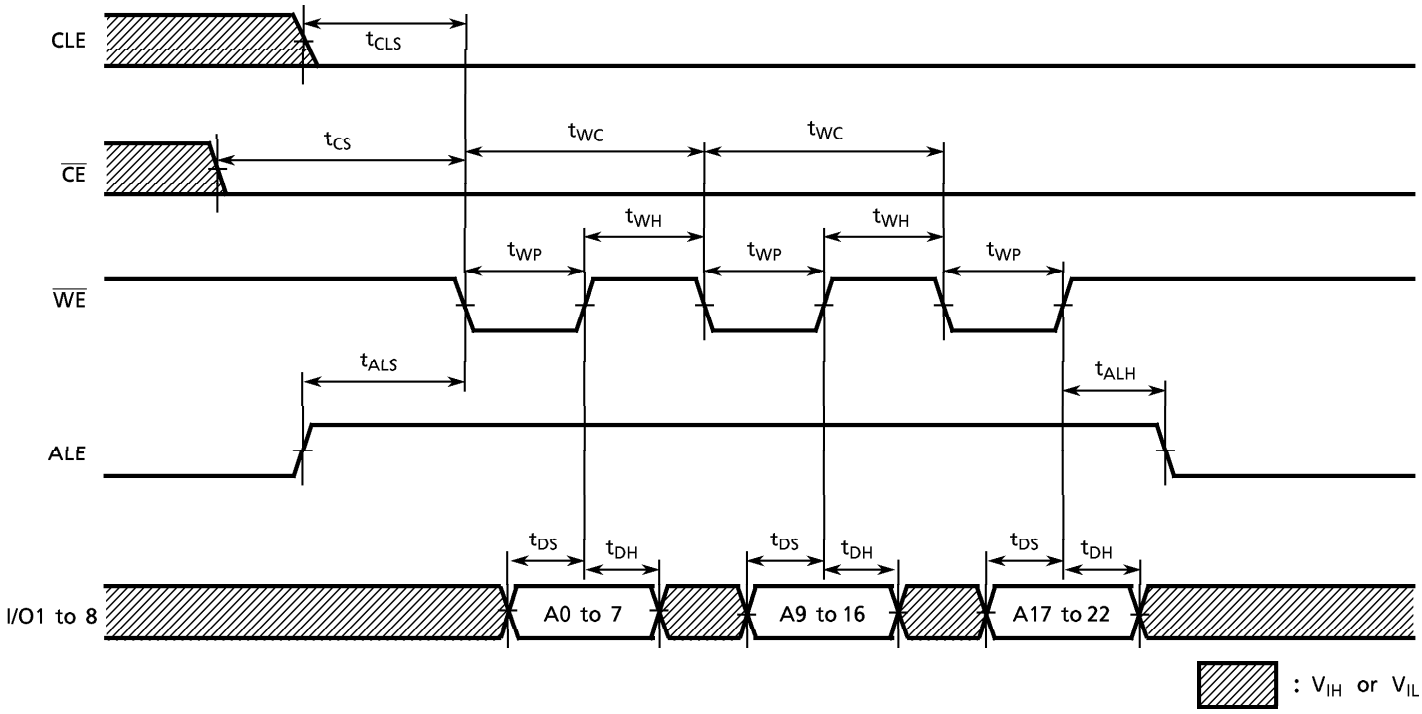
Latch Timing Diagram for Command/Address/Data



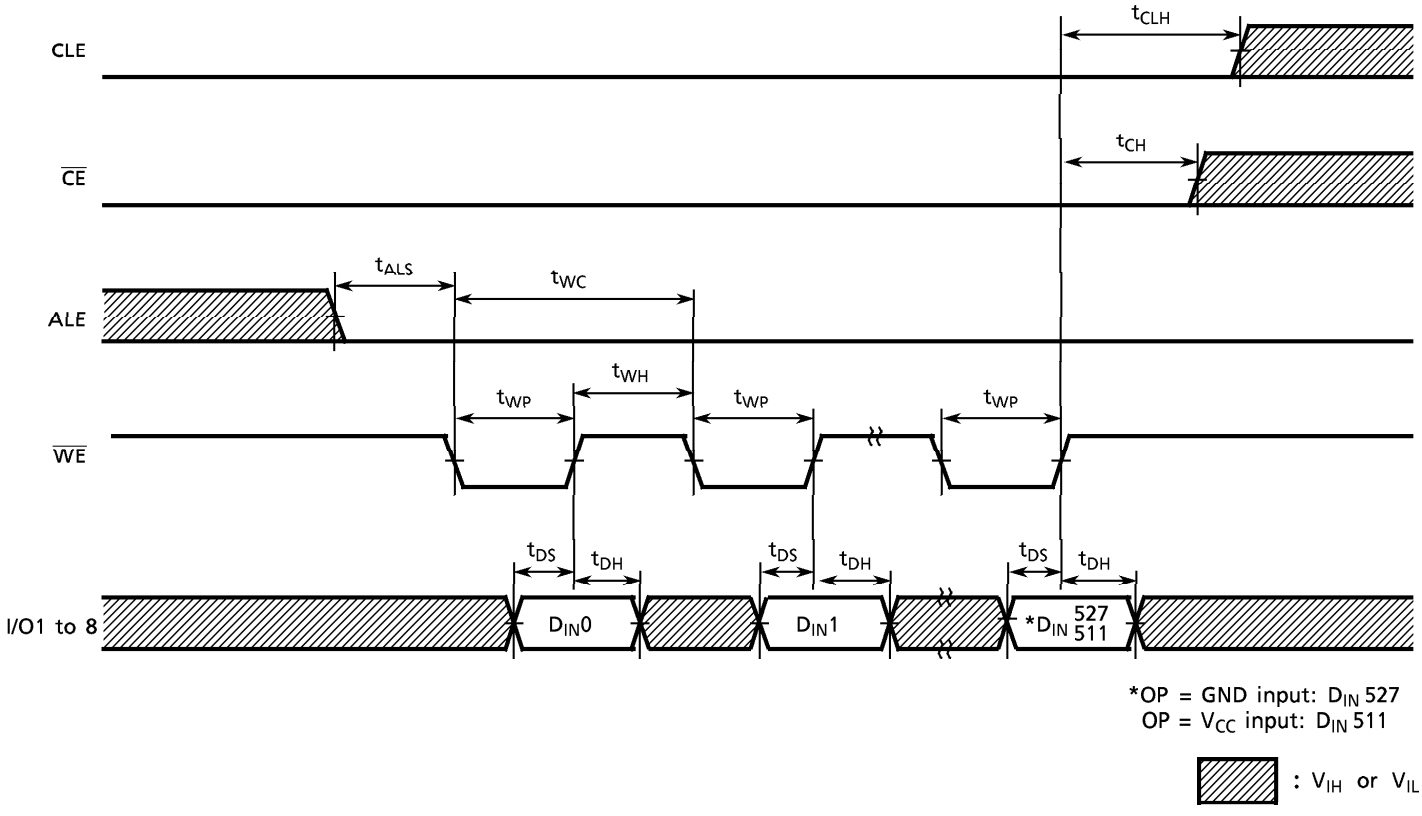
Command Input Cycle Timing Diagram



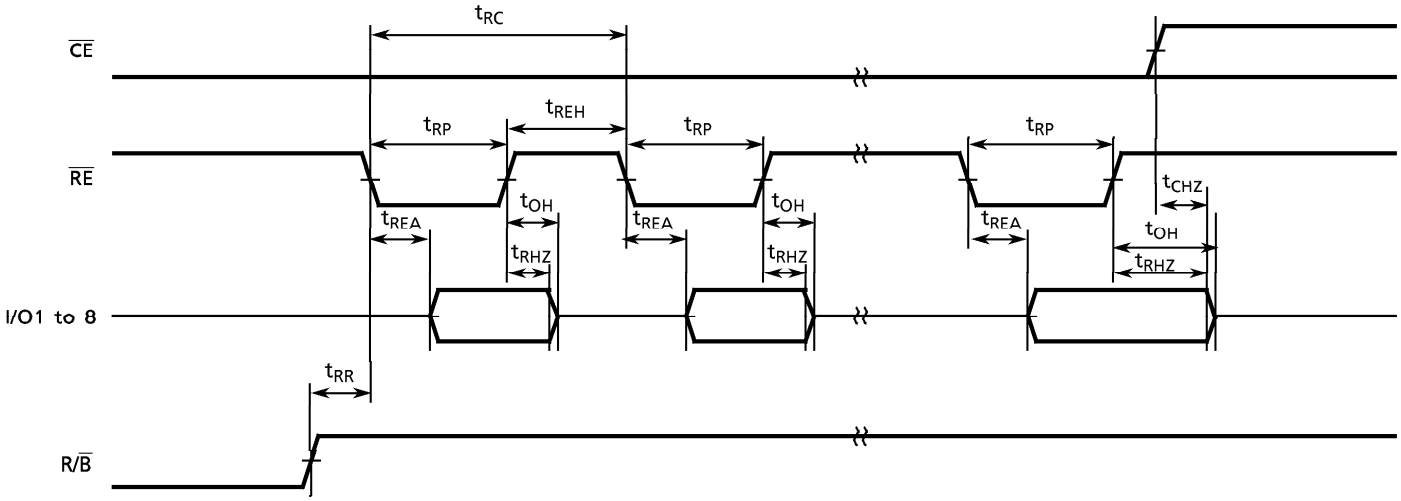
Address Input Cycle Timing Diagram



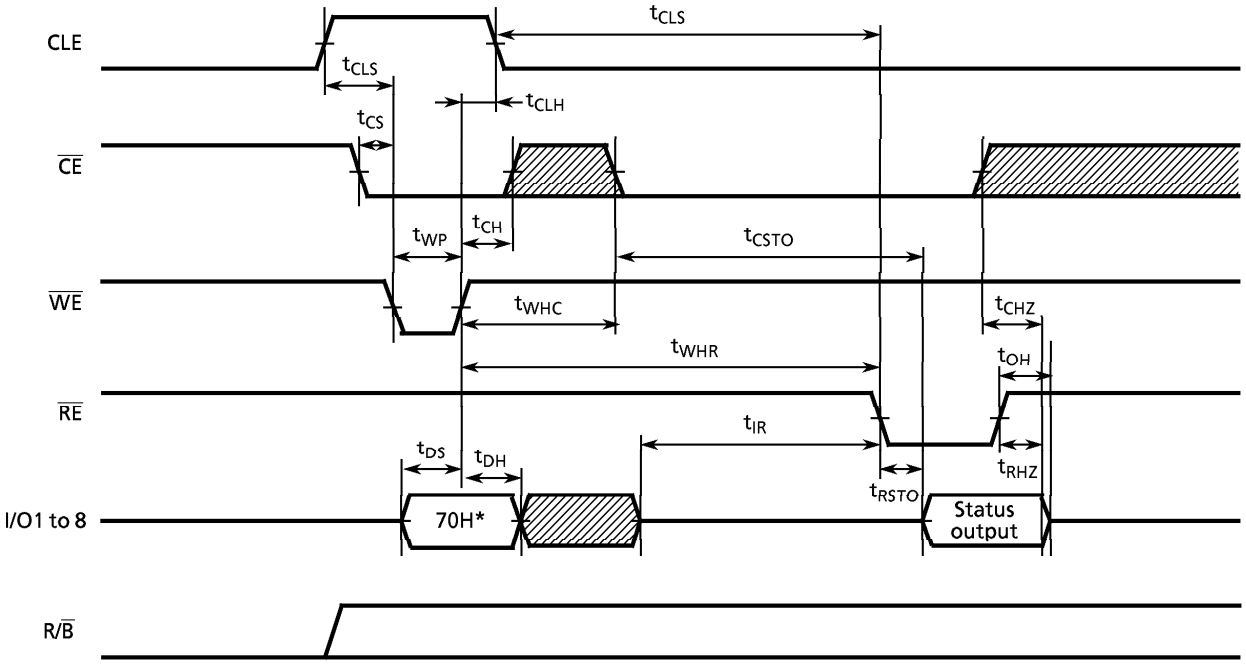
Data Input Cycle Timing Diagram



Serial Read Cycle Timing Diagram



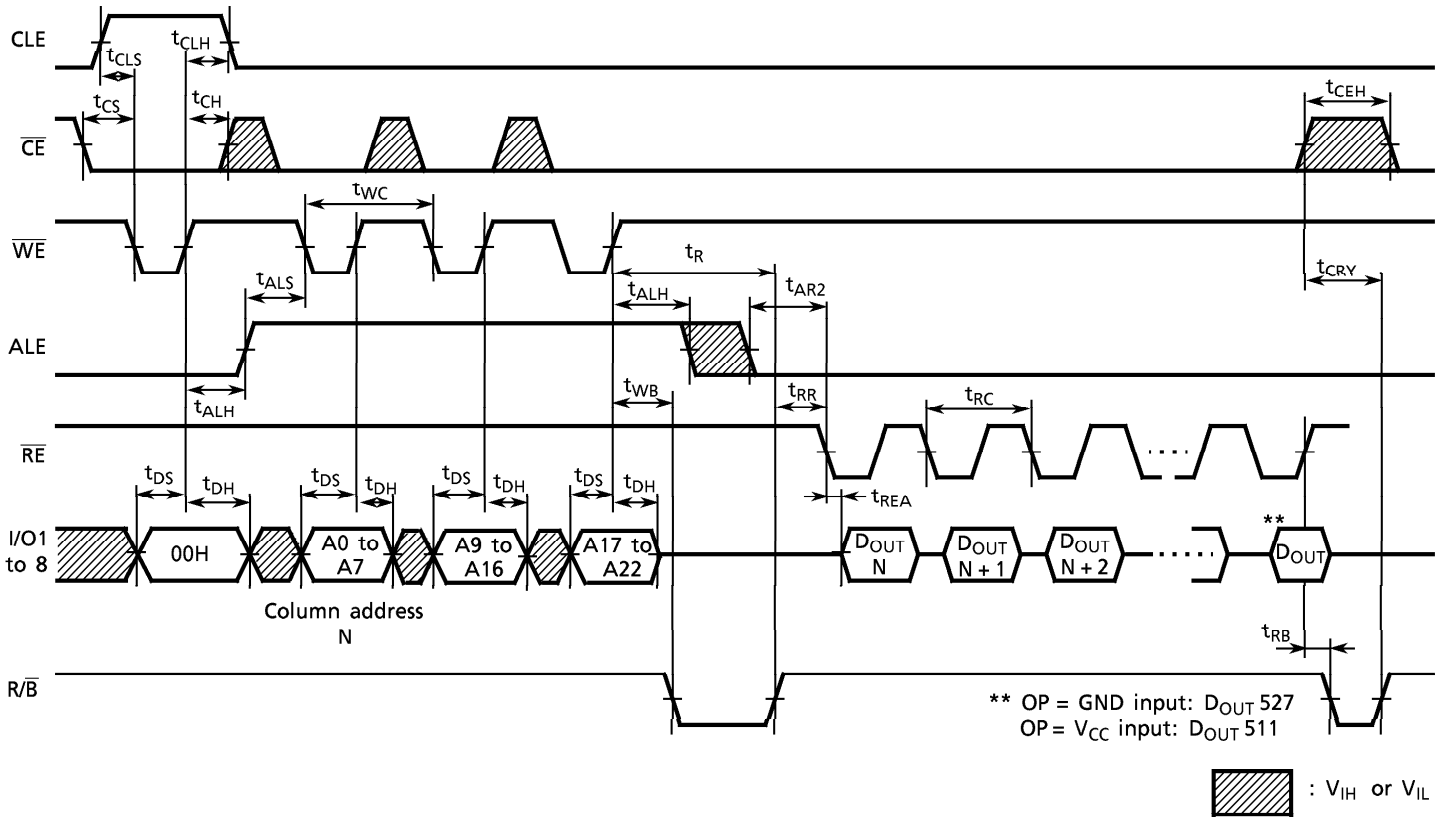
Status Read Cycle Timing Diagram



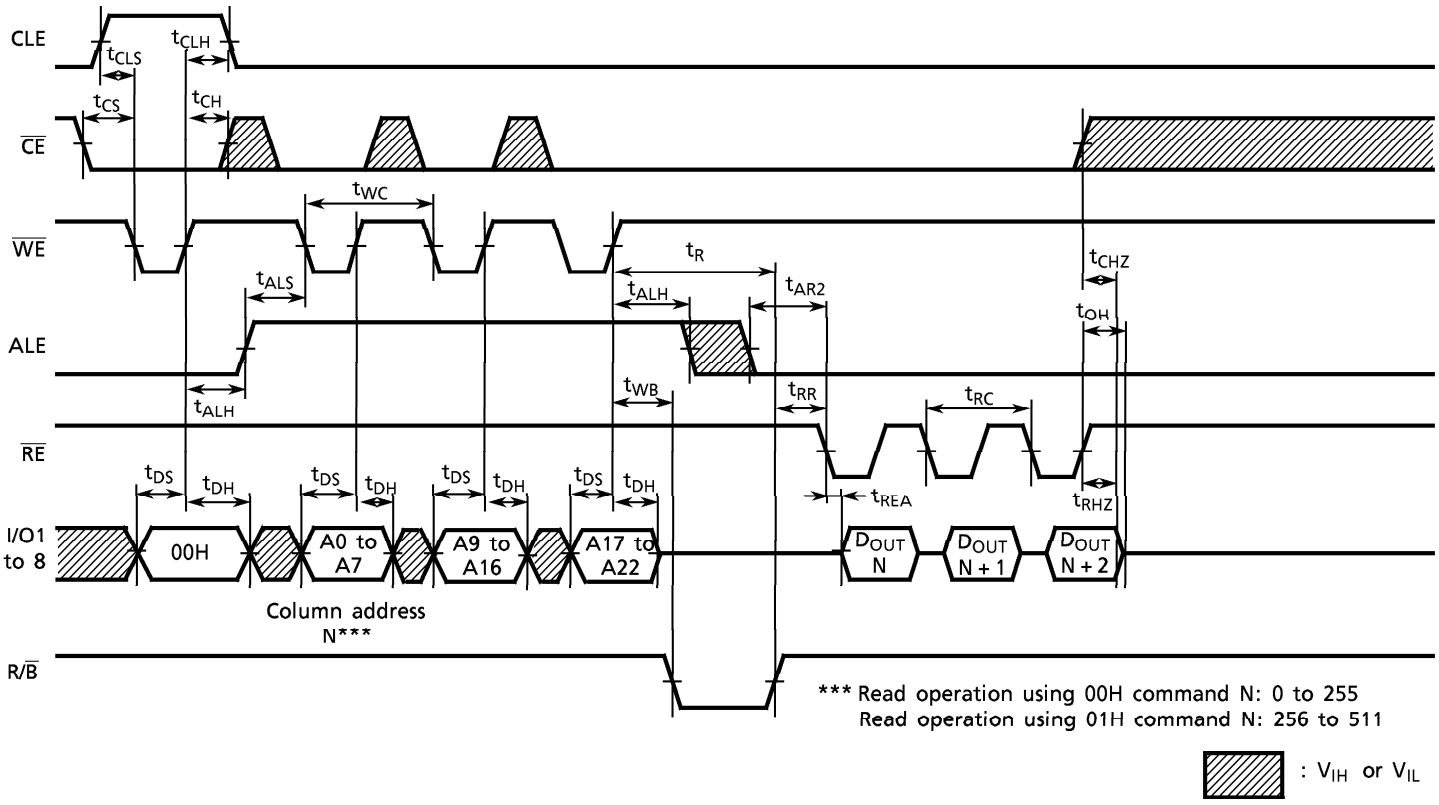
* 70H represents the hexadecimal number 70.

: V_{IH} or V_{IL}

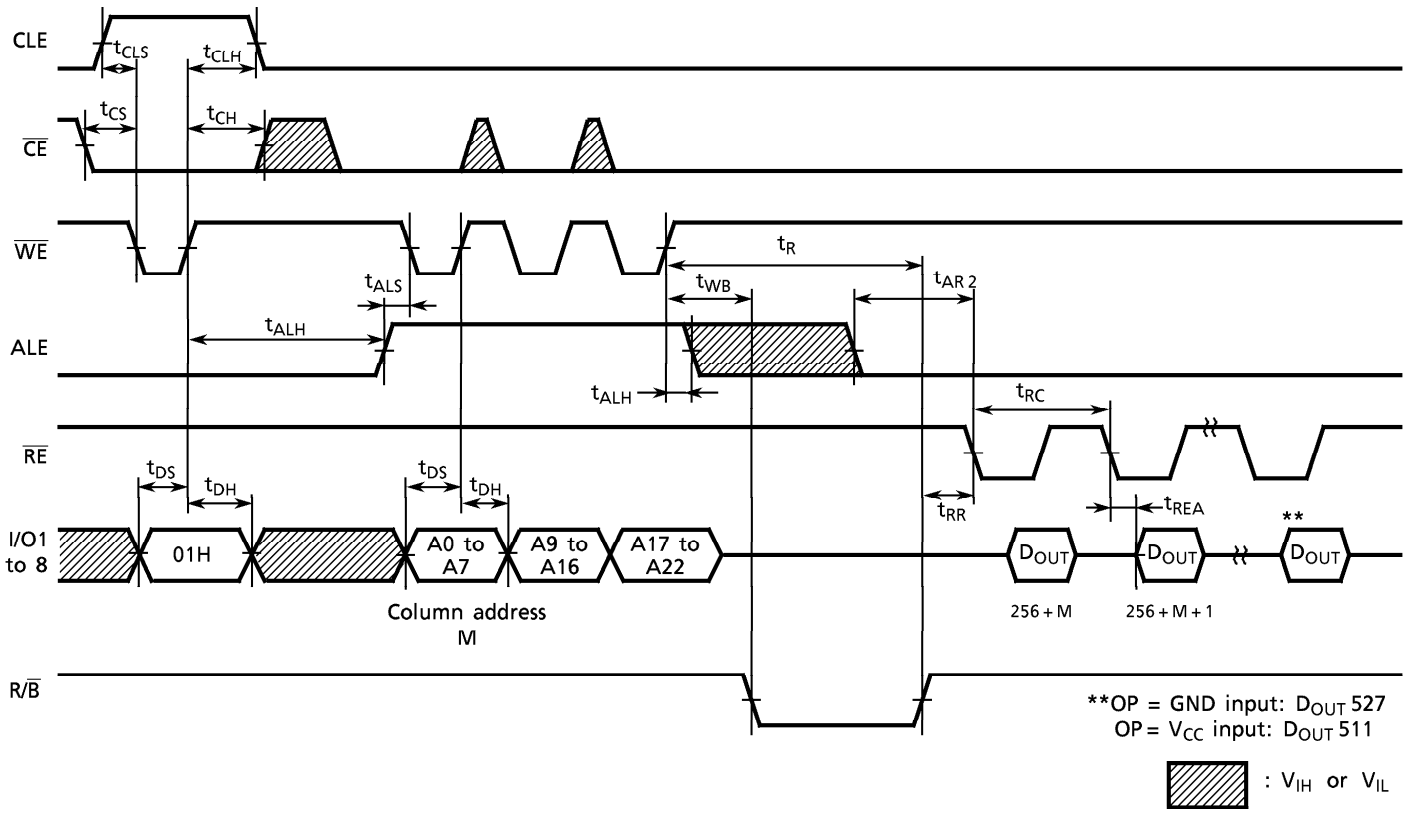
Read Cycle (1) Timing Diagram



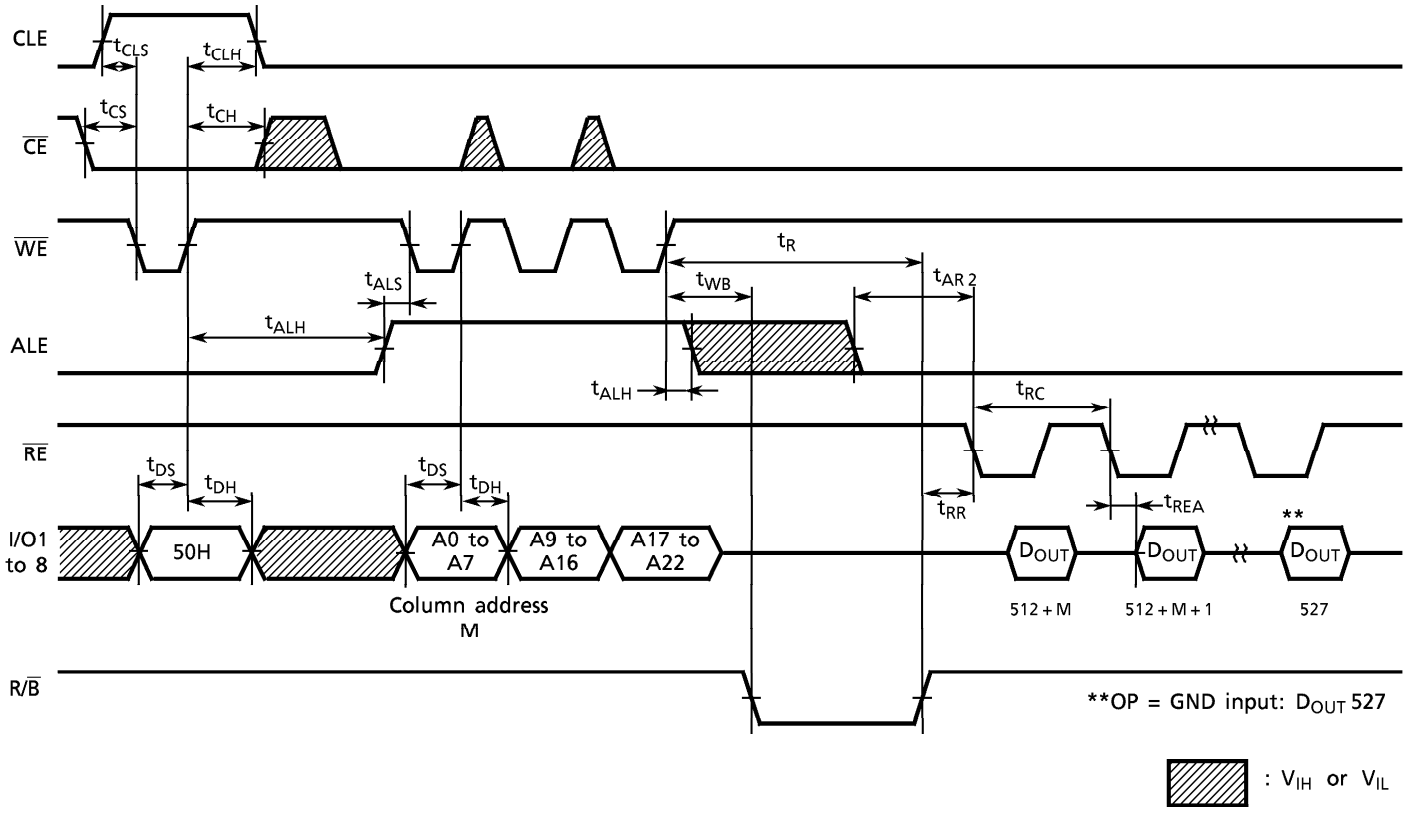
Read Cycle (1) Timing Diagram: When Interrupted by $\overline{CE}$



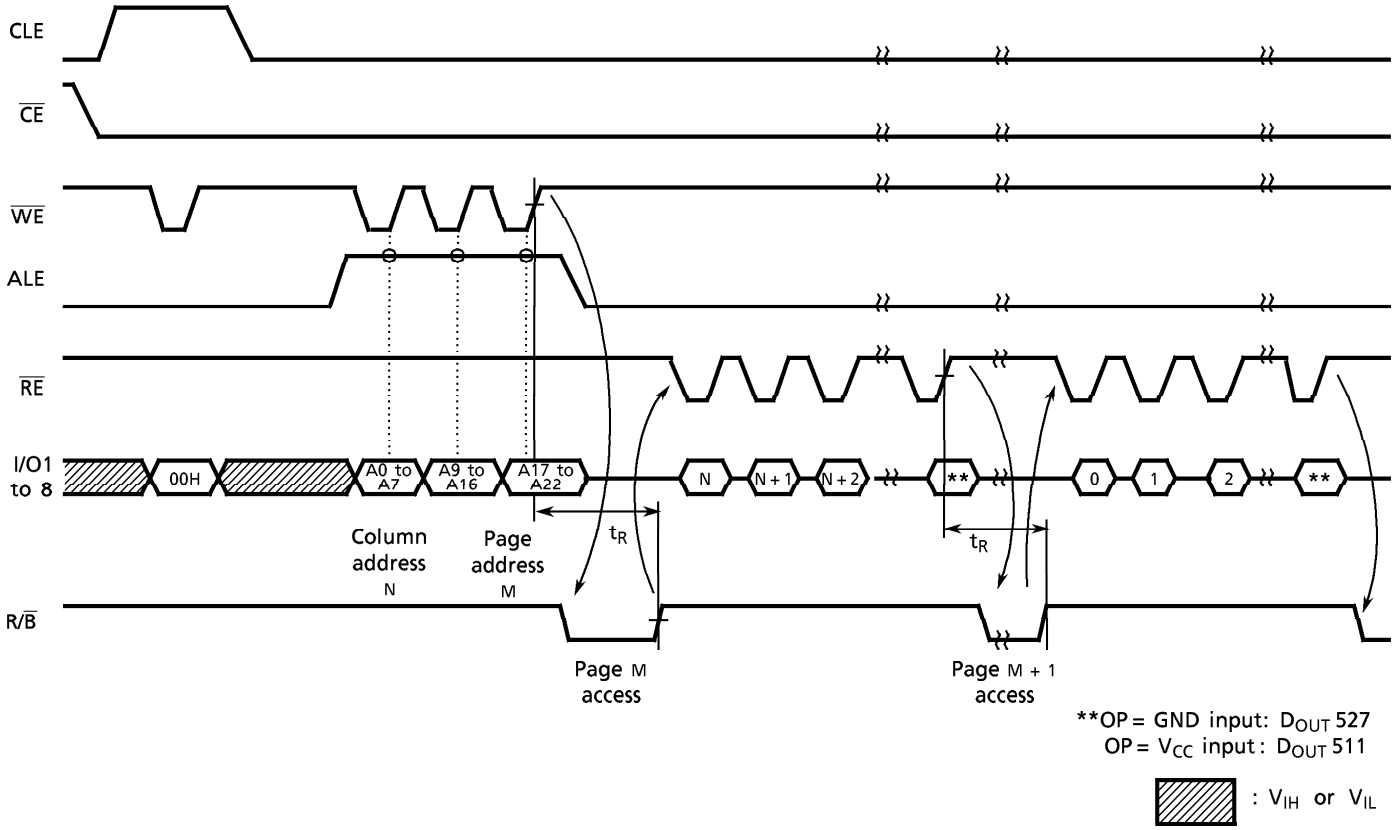
Read Cycle (2) Timing Diagram



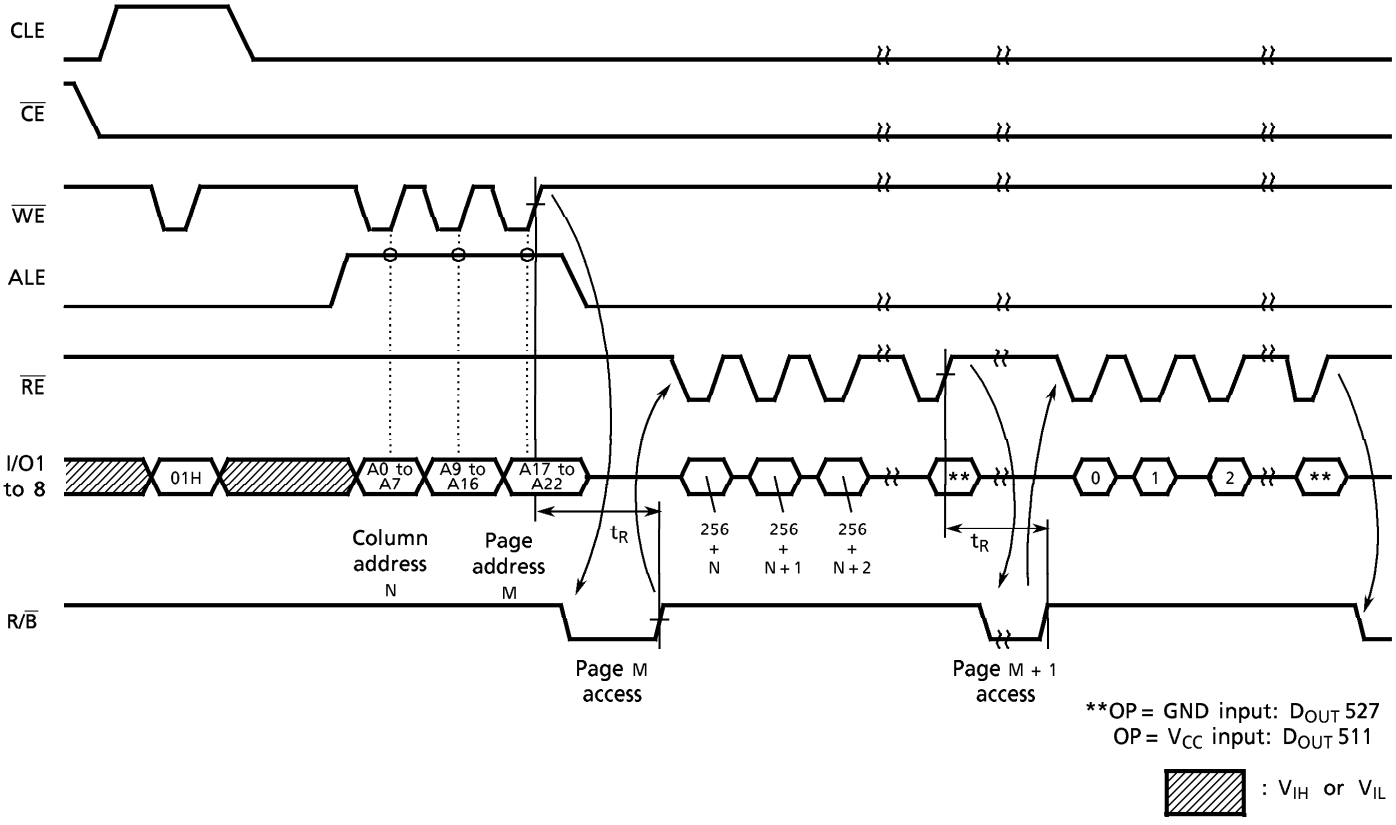
Read Cycle (3) Timing Diagram



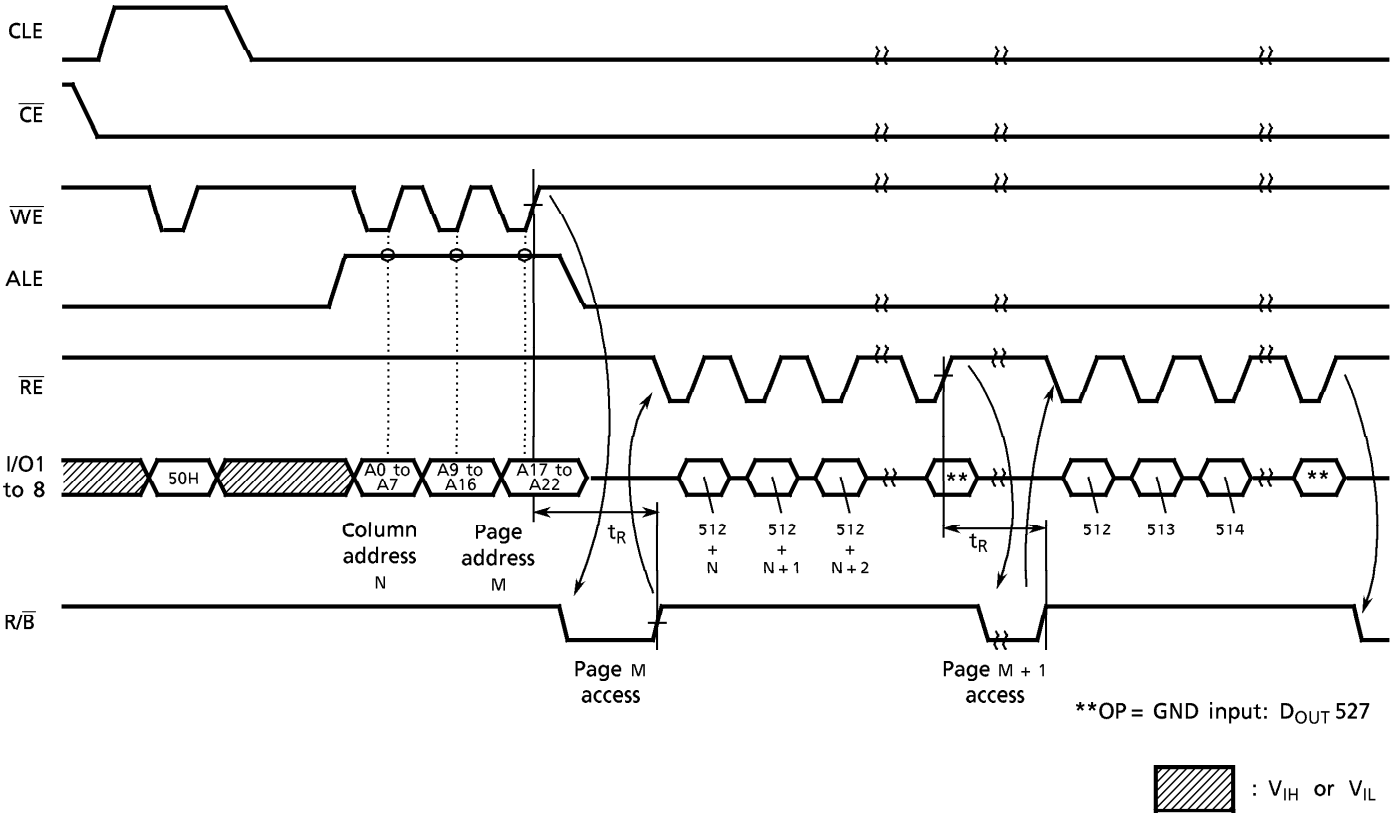
Sequential Read (1) Timing Diagram



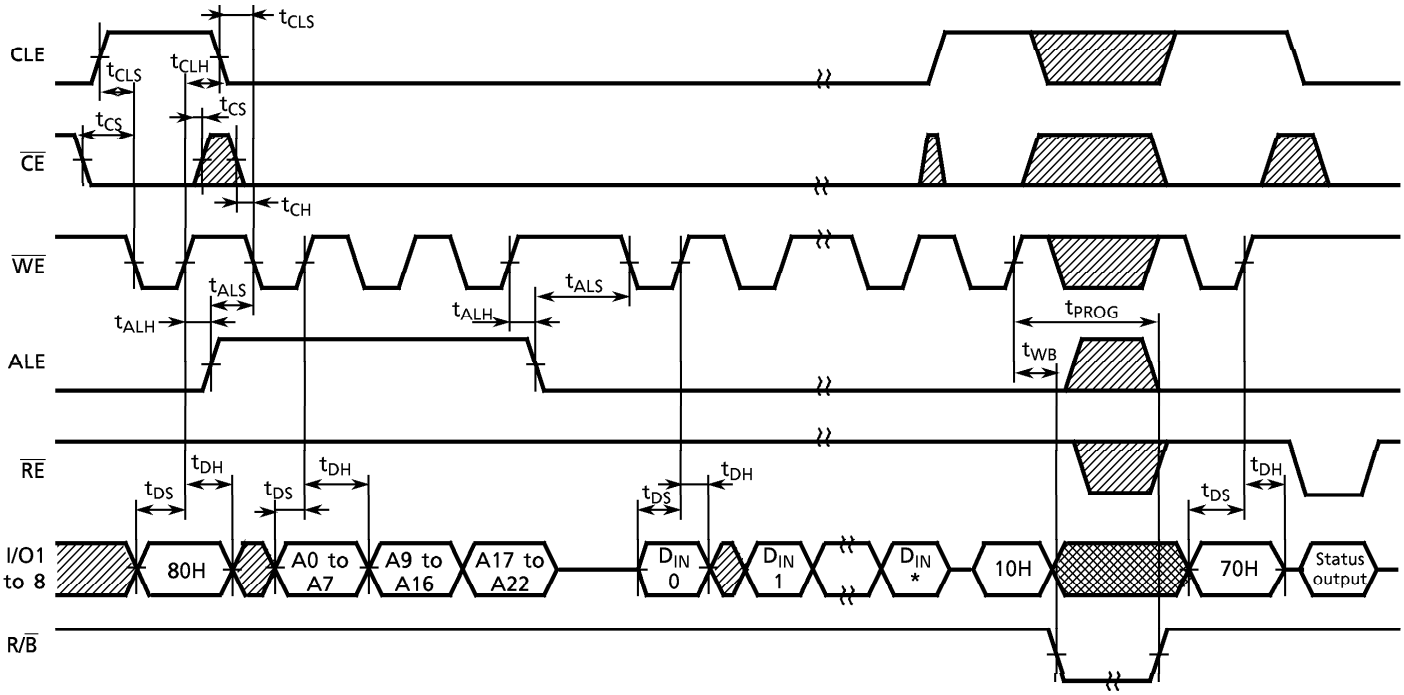
Sequential Read (2) Timing Diagram



Sequential Read (3) Timing Diagram



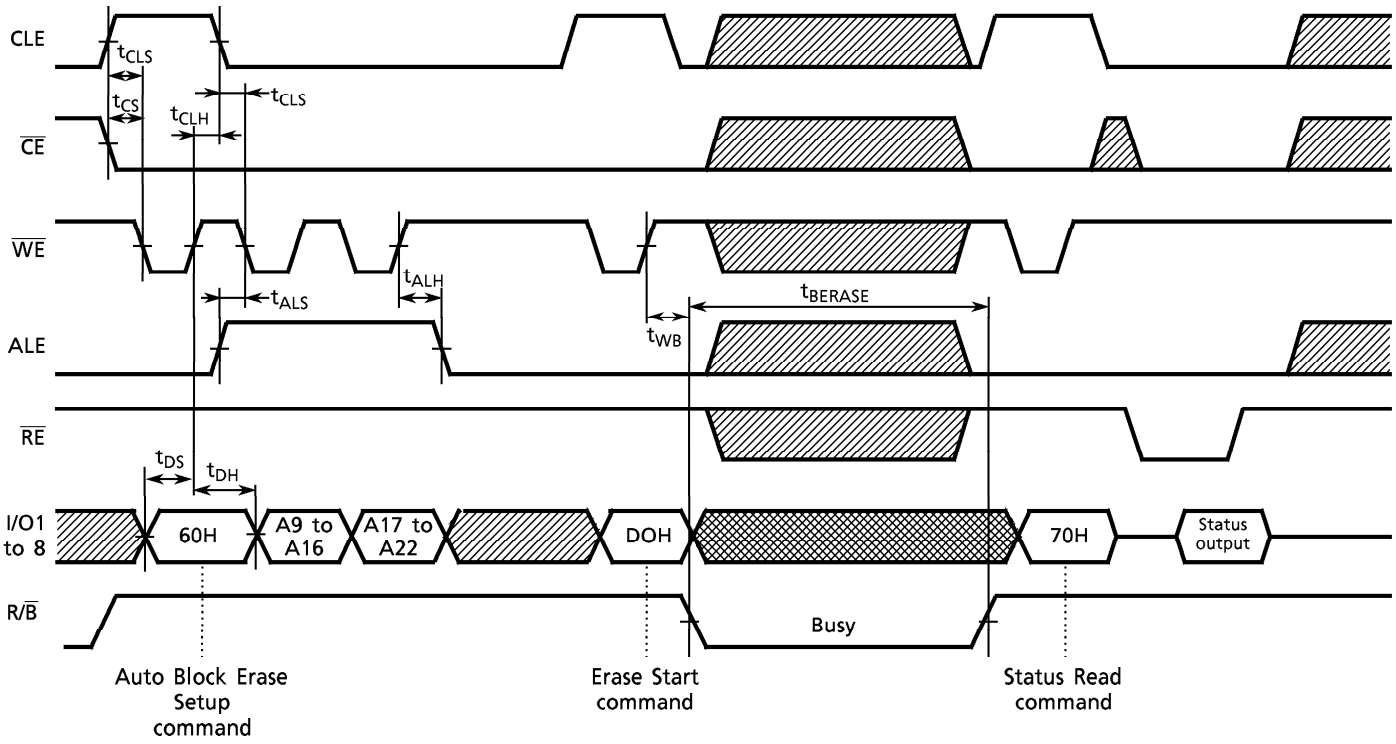
Auto-Program Operation Timing Diagram



*OP = GND input: D_{IN} 527
OP = V_{CC} input: D_{IN} 511

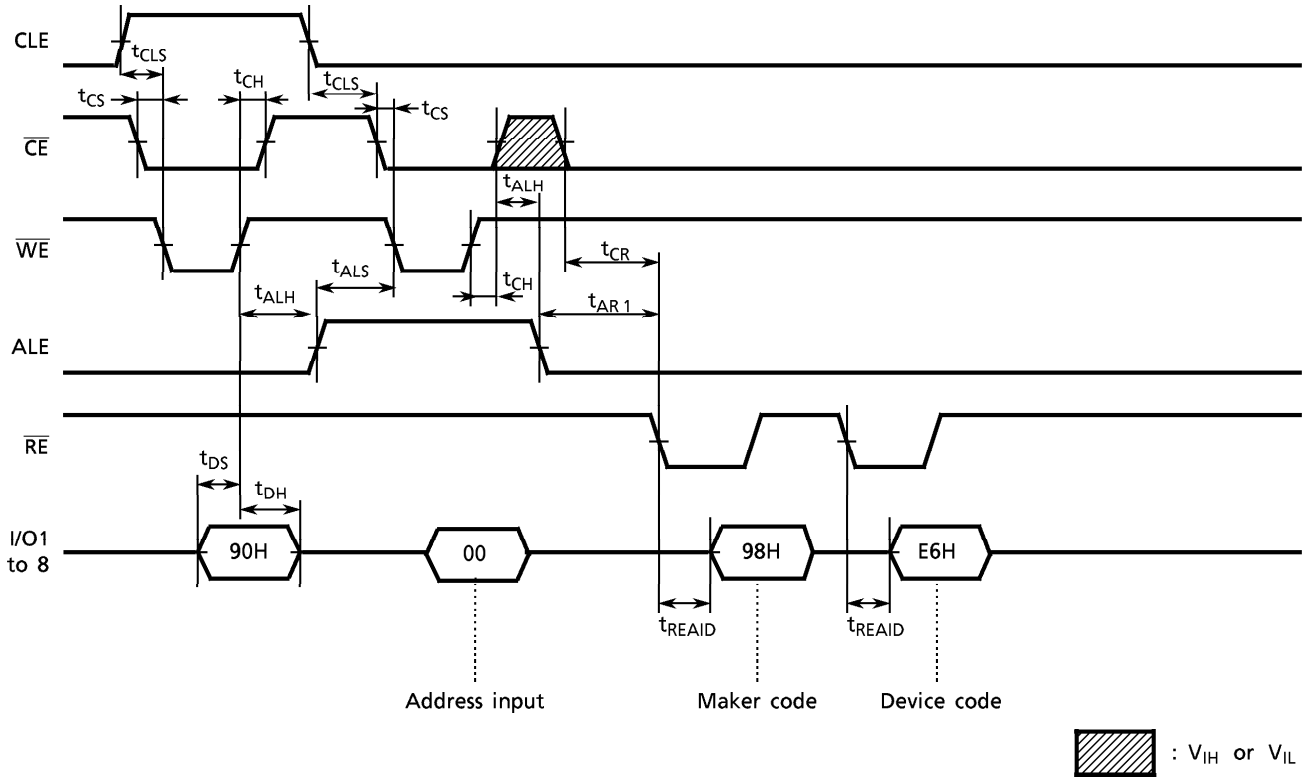
: V_{IH} or V_{IL} : Do not input data while data is being output.

Auto Block Erase Timing Diagram



: V_{IH} or V_{IL} : Do not input data while data is being output.

ID Read Operation Timing Diagram



PIN FUNCTIONS

The device is a serial access memory which utilizes time-sharing input of address information. The device pin-outs are configured as shown in Figure 1.

Command Latch Enable: CLE

The CLE input signal is used to control loading of the operation mode command into the internal command register. The command is latched into the command register from the I/O port on the rising edge of the $\overline{WE}$ signal while CLE is High.

Address Latch Enable: ALE

The ALE signal is used to control loading of either address information or input data into the internal address/data register.
Address information is latched on the rising edge of $\overline{WE}$ if ALE is High. Input data is latched if ALE is Low.

Chip Enable: $\overline{CE}$

The device goes into a low-power Standby mode when $\overline{CE}$ goes High during a Read operation. The $\overline{CE}$ signal is ignored when device is in Busy state (R/$\overline{B}$ = L), such as during a Program or Erase operation, and will not enter Standby mode even if the $\overline{CE}$ input goes High. The $\overline{CE}$ signal must stay Low during the Read mode Busy state to ensure that memory array data is correctly transferred to the data register.

Write Enable: $\overline{WE}$

The $\overline{WE}$ signal is used to control the acquisition of data from the I/O port.

Read Enable: $\overline{RE}$

The $\overline{RE}$ signal controls serial data output. Data is available t_{REA} after the falling edge of $\overline{RE}$.
The internal column address counter is also incremented (Address= Address + 1) on this falling edge.

I/O Port: I/O1 to 8

The I /O1 to 8 pins are used as a port for transferring address, command and input/output data to and from the device.

Write Protect: $\overline{WP}$

The $\overline{WP}$ signal is used to protect the device from accidental programming or erasing. The internal voltage regulator is reset when $\overline{WP}$ is Low. This signal is usually used for protecting the data during the power-on/off sequence when input signals are invalid.

Ready/Busy: R/$\overline{B}$

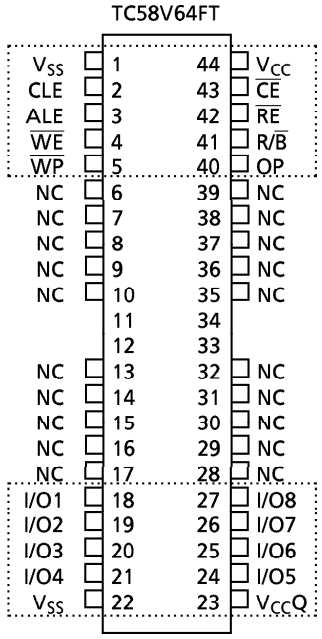
The R/$\overline{B}$ output signal is used to indicate the operating condition of the device. The R/$\overline{B}$ signal is in Busy state (R/$\overline{B}$ = L) during the Program, Erase and Read operations and will return to Ready state (R/$\overline{B}$ = H) after completion of the operation. The output buffer for this signal is an open drain.

Option Pin: OP

The OP signal is used to change the page size. The device is in 528 bytes/page mode when OP = GND and in 512 bytes/page mode when OP = V_{CC}.

Low Voltage Detect: LVD

The LVD signal is used to detect the power supply voltage level. By connecting this pin to V_{SS} via a pull-down resistor, it is possible to distinguish the 3.3-V product (TC58V64DC, TC58V32DC) from the 5-V product (TC5832DC). When a V_{CC} of 3.3-V is applied to pins 12 and 22, an H level can be detected on the system side if the device is a TC58V64DC, and an L level if it is a TC5832DC.



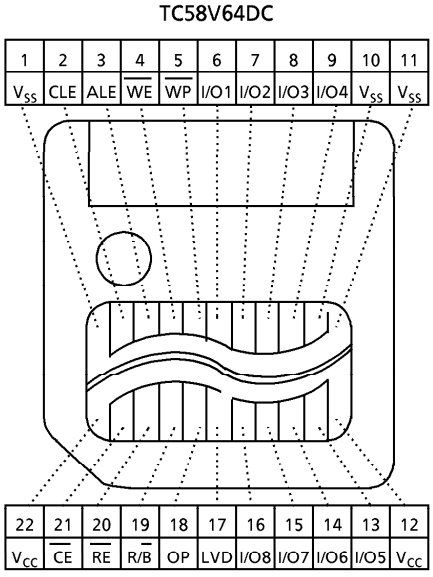


Figure 1. Pinout

Schematic Cell Layout and Address Assignment

The Program operation works on page units while the Erase operation works on block units.

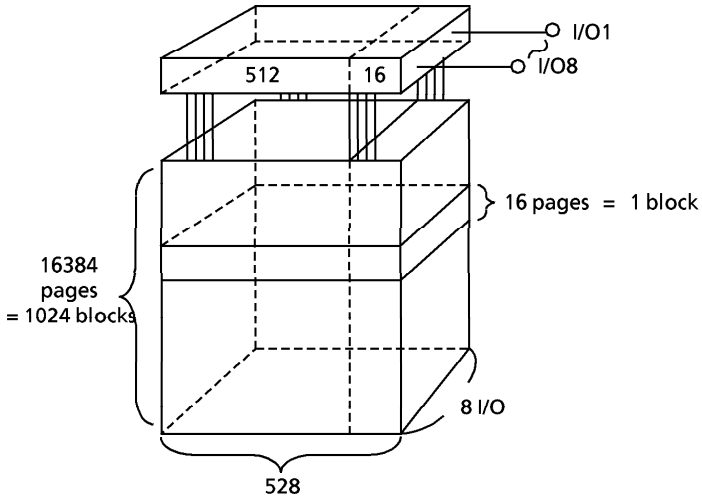


Figure 2. Schematic Cell Layout

A page consists of 528 bytes in which 512 bytes are used for main memory storage and 16 bytes are for redundancy or for other uses.

1 page = 528 bytes
1 block = 528 bytes × 16 pages = (8K + 256) bytes
Capacity = 528 bytes × 16 pages × 1024 blocks

An address is read in via the I/O port over three consecutive clock cycles, as shown in Table 1.

Table 1. Addressing

	I/O1	I/O2	I/O3	I/O4	I/O5	I/O6	I/O7	I/O8
First cycle	A0	A1	A2	A3	A4	A5	A6	A7
Second cycle	A9	A10	A11	A12	A13	A14	A15	A16
Third cycle	A17	A18	A19	A20	A21	A22	* L	* L

A0 to A7: Column address
A9 to A22: Page address
(A13 to A22: Block address
A9 to A12: NAND address in block)

*: A8 is automatically set to Low or High by a 00H command or a 01H command.
*: I/O7 and I/O8 must be set to Low in the third cycle.

Operation Mode: Logic and Command Tables

The operation modes such as Program, Erase, Read and Reset are controlled by the eleven different command operations shown in Table 3. Address input, command input and data input/output are controlled by the CLE, ALE, $\overline{CE}$, $\overline{WE}$, $\overline{RE}$ and $\overline{WP}$ signals, as shown in Table 2.

Table 2. Logic Table

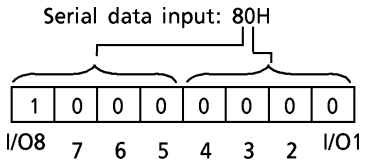
	CLE	ALE	$\overline{CE}$	$\overline{WE}$	$\overline{RE}$	$\overline{WP}$
Command Input	H	L	L	⌐└↗	H	*
Data Input	L	L	L	⌐└↗	H	*
Address Input	L	H	L	⌐└↗	H	*
Serial Data Output	L	L	L	H	↘└⌐	*
During Programming (Busy)	*	*	*	*	*	H
During Erasing (Busy)	*	*	*	*	*	H
Program, Erase Inhibit	*	*	*	*	*	L

H: V_{IH}, L: V_{IL}, *: V_{IH} or V_{IL}

Table 3. Command table (HEX)

	First Cycle	Second Cycle	Acceptable while Busy
Serial Data Input	80	–	
Read Mode (1)	00	–	
Read Mode (2)	01	–	
Read Mode (3)	50	–	
Reset	FF	–	○
Auto Program	10	–	
Auto Block Erase	60	D0	
Status Read	70	–	○
ID Read	90	–	

HEX data bit assignment
(Example)



Once the device has been set to Read mode by a 00H, 01H or 50H command, additional Read commands are not needed for sequential page Read operations. Table 4 shows the operation states for Read mode.

Table 4. Read mode operation states

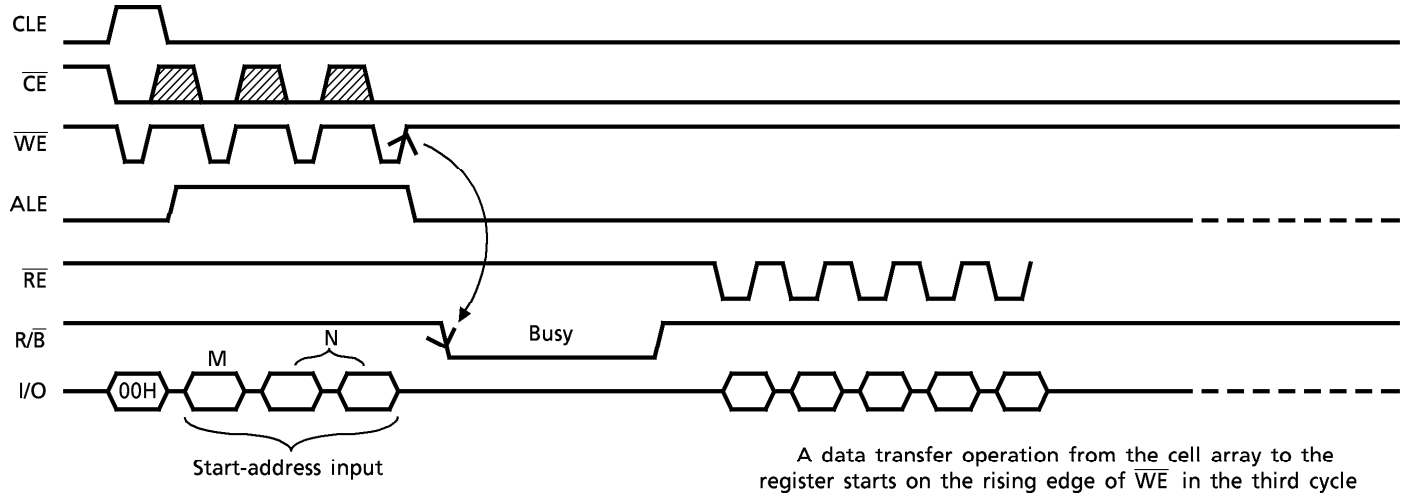
	CLE	ALE	$\overline{CE}$	$\overline{WE}$	$\overline{RE}$	I/O1 TO I/O8	Power
Output Select	L	L	L	H	L	Data output	Active
Output Deselect	L	L	L	H	H	High impedance	Active
Standby	L	L	H	H	*	High impedance	Standby

H: V_{IH} L: V_{IL} *: V_{IH} or V_{IL}

DEVICE OPERATION

Read Mode (1)

Read mode (1) is set when a 00H command is issued to the Command register. Refer to Figure 3 below for timing details and the block diagram.



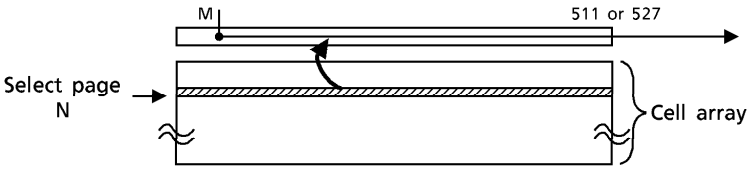
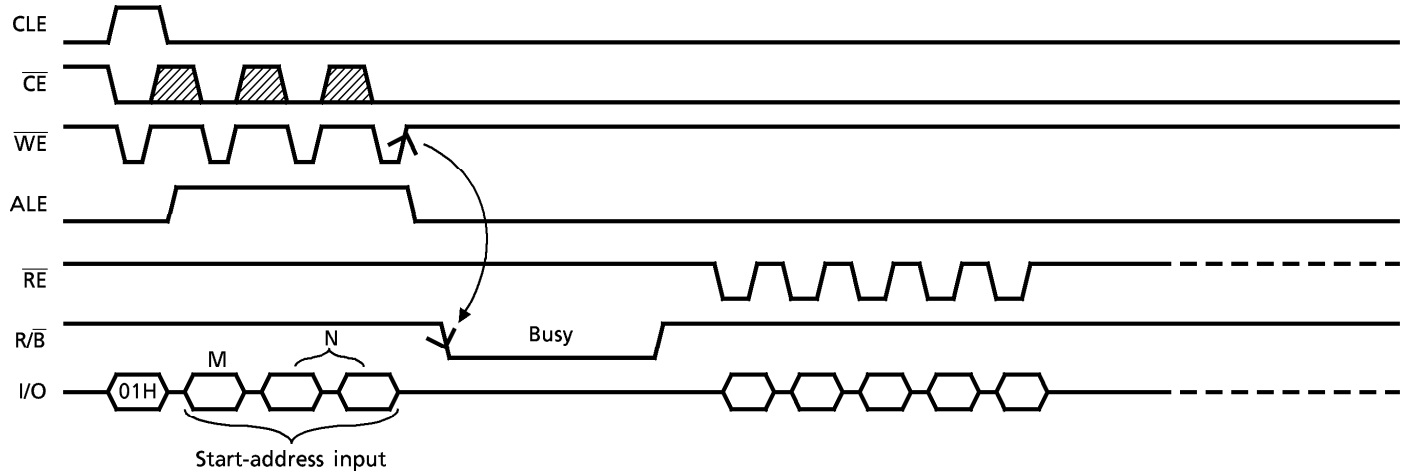


Figure 3. Read mode (1) operation

A data transfer operation from the cell array to the register starts on the rising edge of $\overline{WE}$ in the third cycle (after the address information has been latched). The device will be in Busy state during this transfer period. The $\overline{CE}$ signal must stay Low after the third address input and during Busy state.

After the transfer period the device returns to Ready state. Serial data can be output synchronously with the $\overline{RE}$ clock from the start pointer designated in the address input cycle.

Read Mode (2)



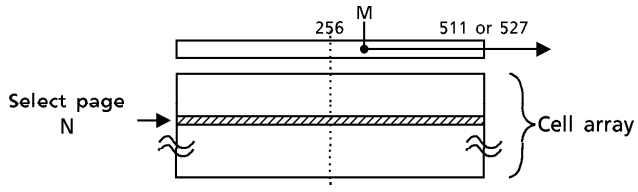


Figure 4. Read mode (2) operation

The operation of the device after input of the 01H command is the same as that of Read mode (1). If the start pointer is to be set after column address 256, use Read mode (2).

However, for a Sequential Read, output of the next page starts from column address 0.

Read Mode (3)

Read mode (3) has the same timing as Read modes (1) and (2) but is used to access information in the extra 16-byte redundancy area of the page. The start pointer is therefore set to a value between byte 512 and byte 527.

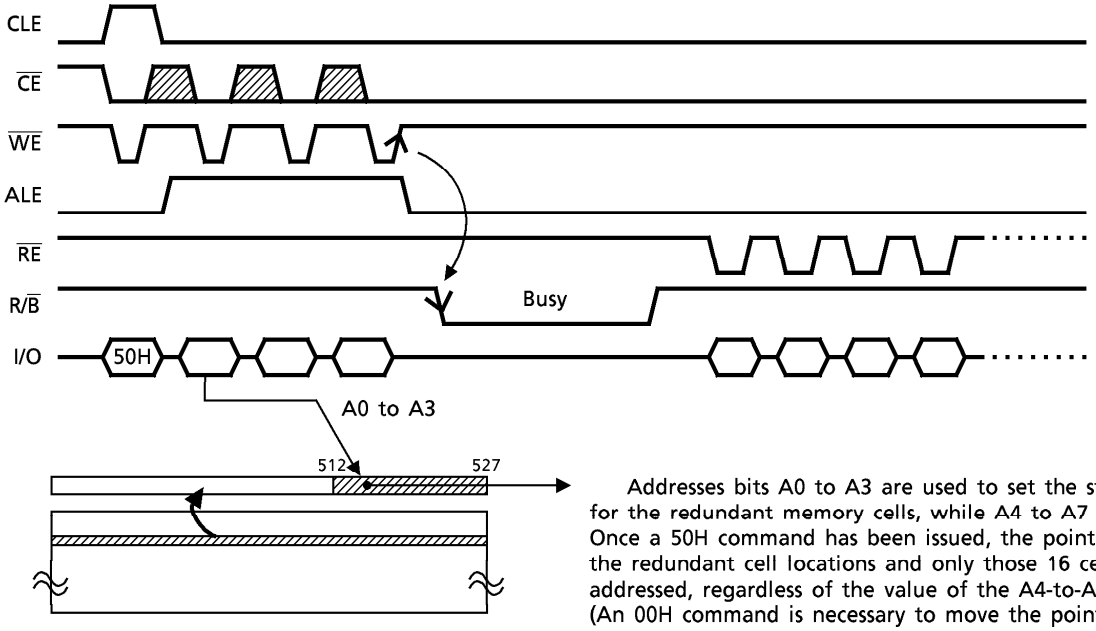
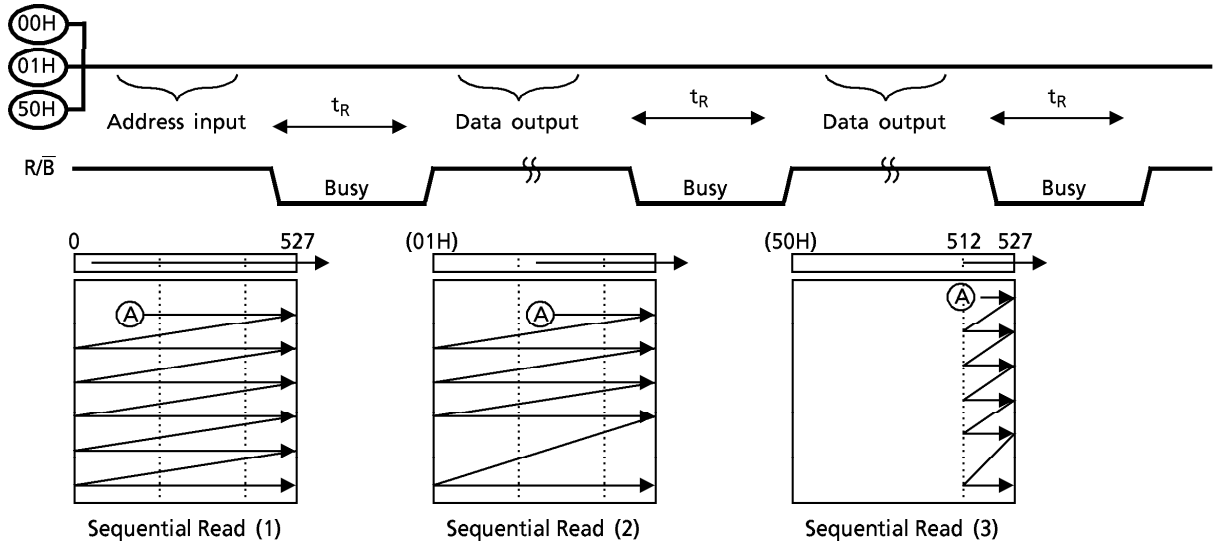


Figure 5. Read mode (3) operation

Addresses bits A0 to A3 are used to set the start pointer for the redundant memory cells, while A4 to A7 are ignored. Once a 50H command has been issued, the pointer moves to the redundant cell locations and only those 16 cells can be addressed, regardless of the value of the A4-to-A7 address. (An 00H command is necessary to move the pointer back to the 0-to-511 main memory cell location.)
Read mode (3) operation is invalid when OP is at the V_{CC} level.

Sequential Read (1)(2)(3)

This mode allows the sequential reading of pages without additional address input.



Sequential Read modes (1) and (2) output the contents of addresses 0 to 527 as shown above, while Sequential Read mode (3) outputs the contents of the redundant address locations only. When the pointer reaches the last address, the device continues to output the data from this address ** on each $\overline{RE}$ clock signal.

** OP = GND: column address 527
OP = V_{CC}: column address 511

Status Read

The device automatically implements the execution and verification of the Program and Erase operations. The Status Read function is used to monitor the Ready/Busy status of the device, determine the result (pass/fail) of a Program or Erase operation, and determine whether the device is in Suspend or Protect mode. The device status is output via the I/O port on the $\overline{RE}$ clock after a 70H command input. The resulting information is outlined in Table 5.

Table 5. Status output table

	STATUS	OUTPUT
I/O1	Pass/Fail	Pass: 0 Fail: 1
I/O2	Not Used	0
I/O3	Not Used	0
I/O4	Not Used	0
I/O5	Not Used	0
I/O6	Not Used	0
I/O7	Ready/Busy	Ready: 1 Busy: 0
I/O8	Write Protect	Protect: 0 Not Protected: 1

The Pass/Fail status on I/O1 is only valid when the device is in the Ready state.

An application example with multiple devices is shown in Figure 6.

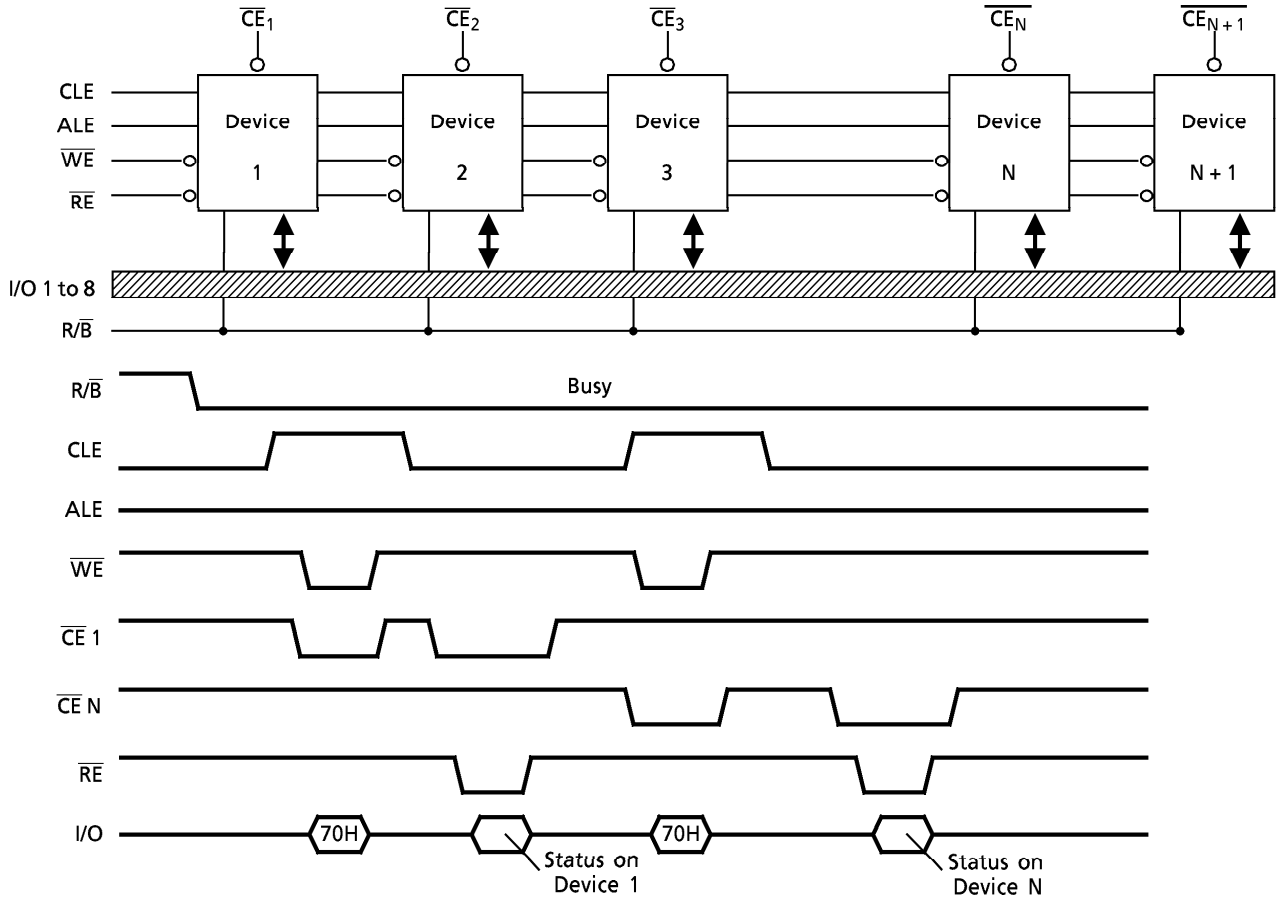


Figure 6. Status Read timing application example

System Design Note: If the R/$\overline{B}$ pin signals from multiple devices are wired together as shown in the diagram, the Status Read function can be used to determine the status of each individual device.

Auto Page Program

The device carries out an Automatic Page Program operation when it receives a 10H Program command after the address and data have been input. The sequence of command, address and data input is shown below. (Refer to the detailed timing chart.)

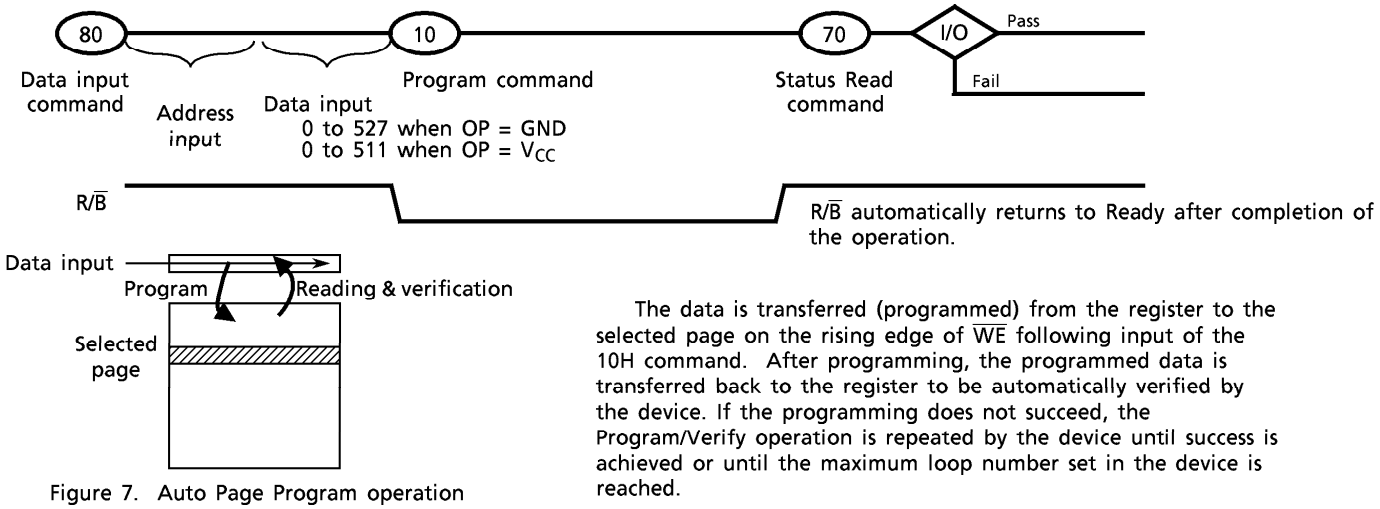
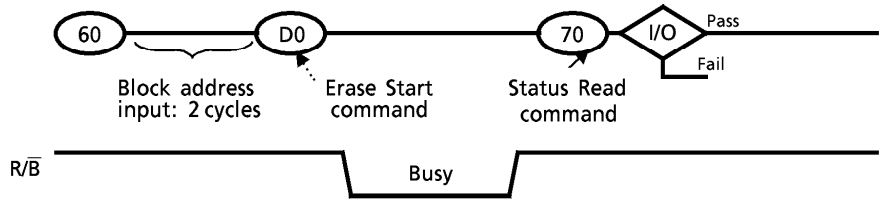


Figure 7. Auto Page Program operation

The data is transferred (programmed) from the register to the selected page on the rising edge of $\overline{WE}$ following input of the 10H command. After programming, the programmed data is transferred back to the register to be automatically verified by the device. If the programming does not succeed, the Program/Verify operation is repeated by the device until success is achieved or until the maximum loop number set in the device is reached.

Auto Block Erase

The Auto Block Erase operation starts on the rising edge of $\overline{WE}$ after the Erase Start command D0H which follows the Erase Setup command 60H. This two-cycle process for Erase operations acts as an extra layer of protection from accidental erasure of data due to external noise. The device automatically executes the Erase and Verify operations.



Reset

The Reset mode stops all operations. For example, in the case of a Program or Erase operation the internally generated voltage is discharged to 0 V and the device enters Wait state. The address and data registers are set as follows after a Reset:

- Address Register: All 0s
- Data Register: All 1s
- Operation Mode: Wait state

The response to an FFH Reset command input during the various device operations is as follows:

- When a Reset (FFH) command is input during programming

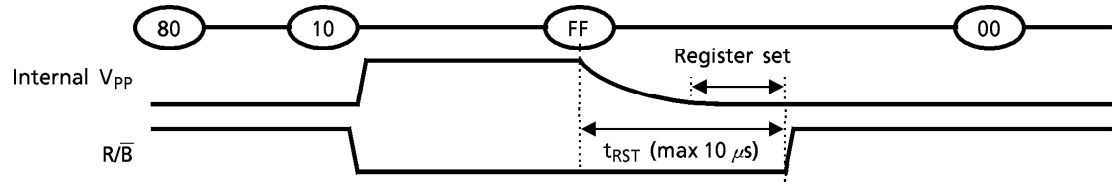


Figure 8.

- When a Reset (FFH) command is input during erasing

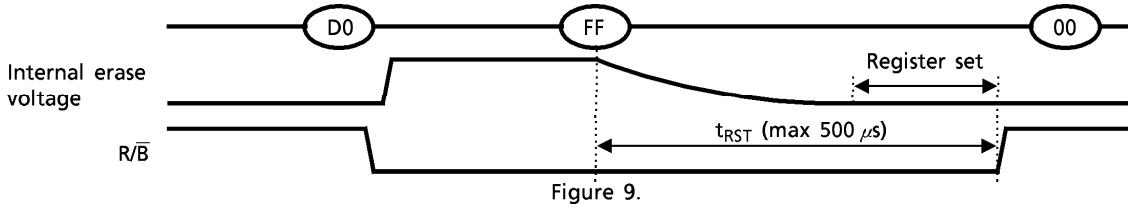


Figure 9.

- When a Reset (FFH) command is input during a Read operation

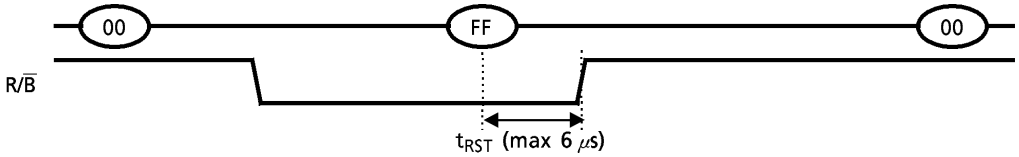


Figure 10.

- When a Status Read command (70H) is input after a Reset

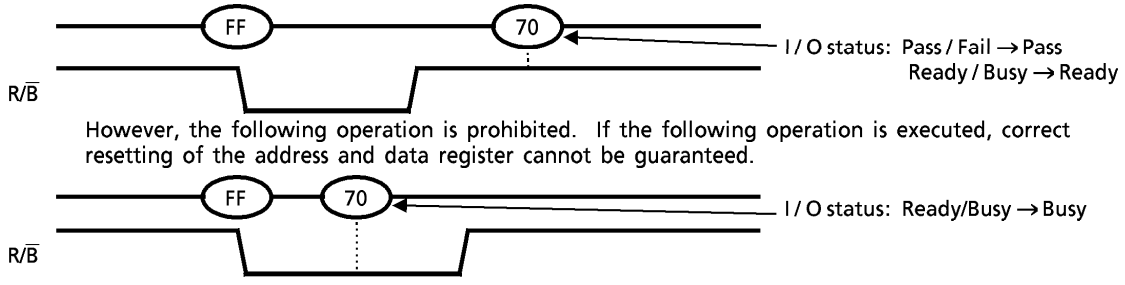


Figure 11.

- When two or more Reset commands are input in succession

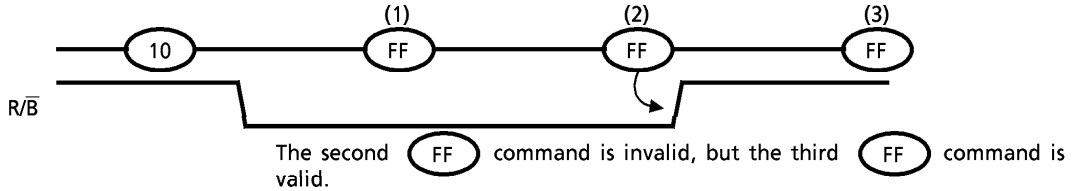


Figure 12.

ID Read

The TC58V64FT/DC contains ID codes which identify the device type and the manufacturer. The ID codes can be read out under the following timing conditions:

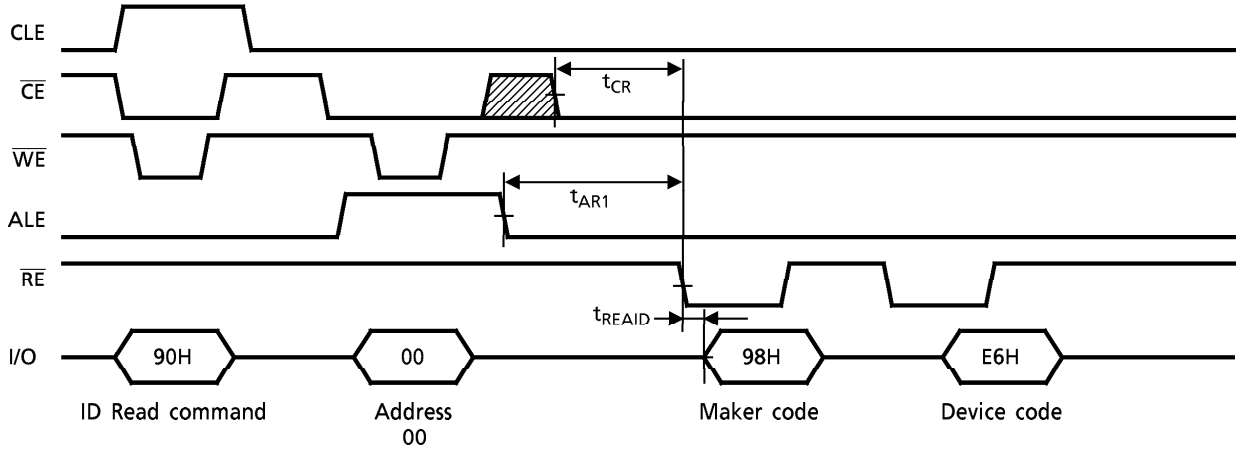


Figure 13. ID Read timing

For the specifications of the access times t_{REAID}, t_{CR} and t_{AR1} refer to the AC Characteristics.

Table 6. Code table

	I/O8	I/O7	I/O6	I/O5	I/O4	I/O3	I/O2	I/O1	Hex Data
Maker code	1	0	0	1	1	0	0	0	98H
Device code	1	1	1	0	0	1	1	0	E6H

APPLICATION NOTES AND COMMENTS

(1) Prohibition of unspecified commands

The operation commands are listed in Table 3. Input of a command other than those specified in Table 3 is prohibited. Stored data may be corrupted if an unknown command is entered during the command cycle.

(2) Pointer control for 00H, 01H and 50H

The device has three Read modes which set the destination of the pointer. Table 7 shows the destination of the pointer, and Figure 14 is a block diagram of their operations.

Table 7. Pointer Destination

Read Mode	Command	Pointer
(1)	00H	0 to 255
(2)	01H	256 to 511
(3)	50H	512 to 527

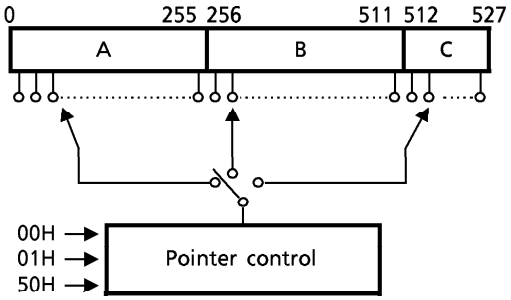
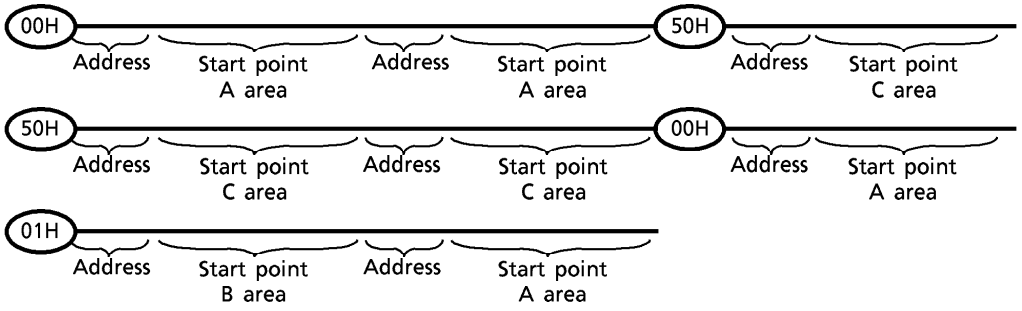


Figure 14. Pointer control

The pointer is set to region A by the 00H command, to region B by the 01H command, and to region C by the 50H command.

(Example)

The 00H command must be input to set the pointer back to region A when the pointer is pointing to region C.



To program region C only, set the start point to region C using the 50H command.

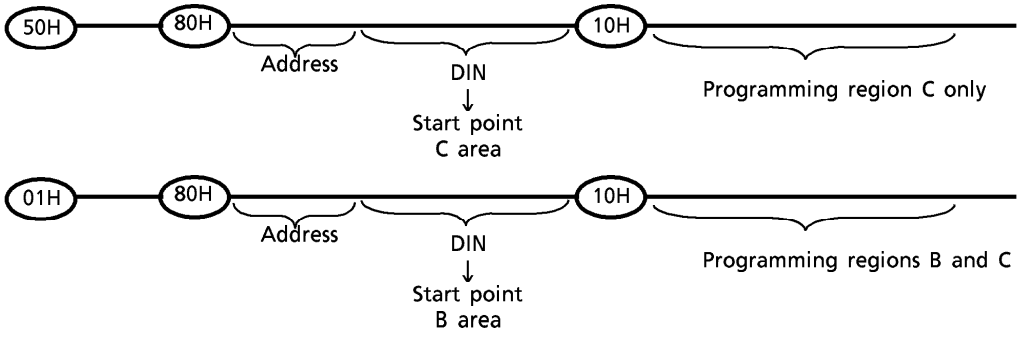


Figure 15. Example of How to Set the Pointer

(3) Acceptable commands after Serial Input command 80H

Once the Serial Input command 80H has been input, do not input any command other than the Program Execution command 10H or the Reset command FFH.

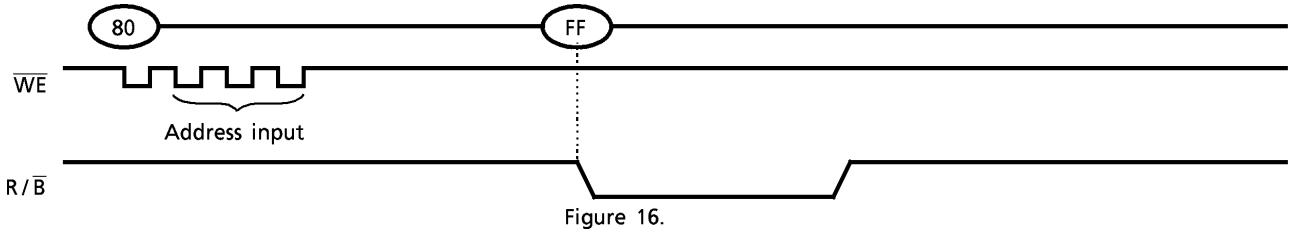
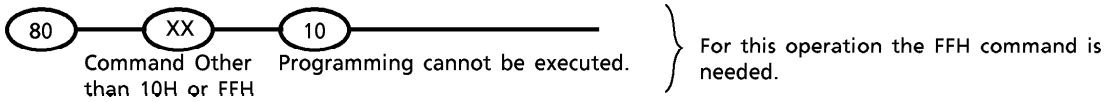


Figure 16.

If a command other than 10H or FFH is input, the Program operation is not performed.



(4) Status Read during a Read operation

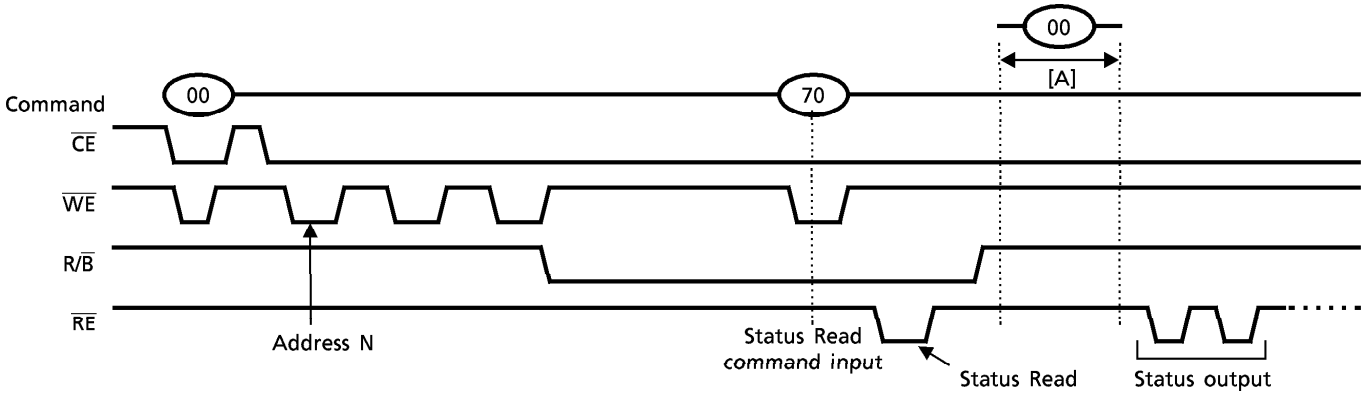


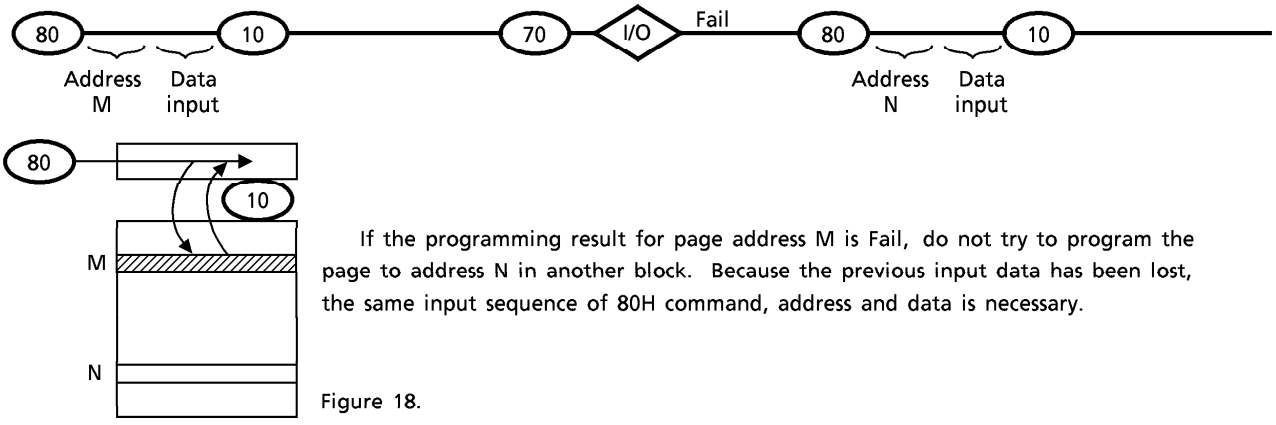
Figure 17.

The device status can be read out by inputting the Status Read command 70H in Read mode. Once the device has been set to Status Read mode by a 70H command, the device will not return to Read mode.

Therefore, a Status Read during a Read operation is prohibited.

However, when the Read command 00H is input during [A], Status mode is reset and the device returns to Read mode. In this case, data output starts automatically from address N and address input is unnecessary .

(5) Auto programming failure



If the programming result for page address M is Fail, do not try to program the page to address N in another block. Because the previous input data has been lost, the same input sequence of 80H command, address and data is necessary.

Figure 18.

(6) R/$\overline{B}$: termination for the Ready/Busy pin (R/$\overline{B}$)

A pull-up resistor needs to be used for termination because the R/$\overline{B}$ buffer consists of an open drain circuit.

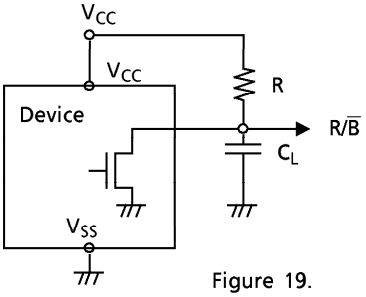
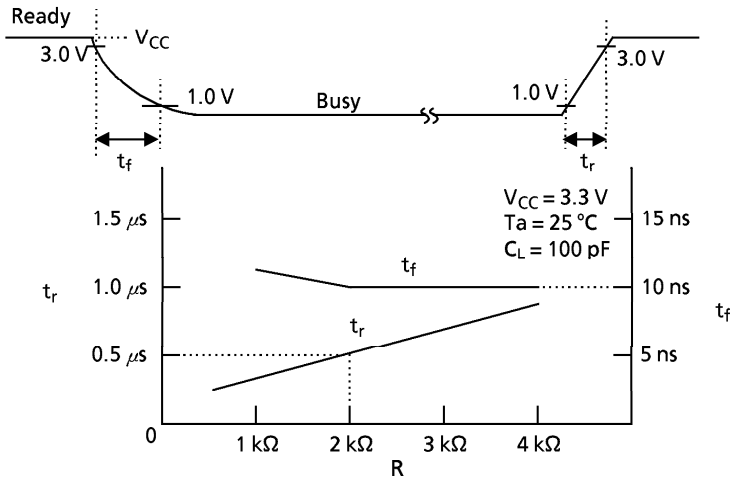


Figure 19.

This data may vary from device to device. We recommend that you use this data as a reference when selecting a resistor value.



(7) Status after power-on

Although the device is set to Read mode after power-on, the following sequence is necessary because some input signals may not be stable at power-on.

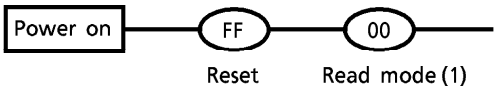


Figure 20.

(8) Power-on/off sequence:

The $\overline{WP}$ signal is useful for protecting against data corruption at power-on/off. The following timing sequence is necessary:

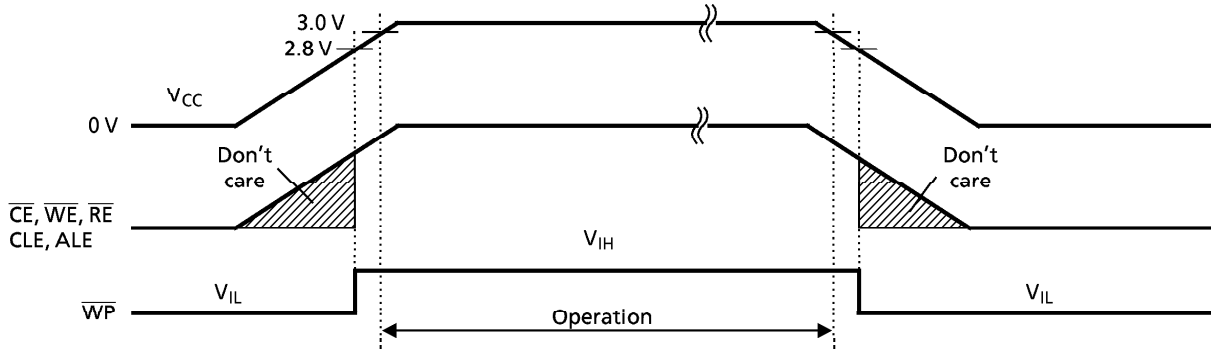
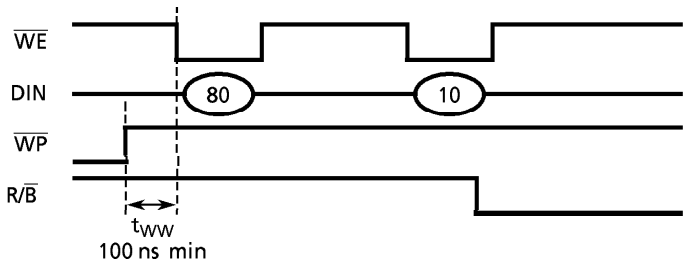


Figure 21. Power-on/off Sequence

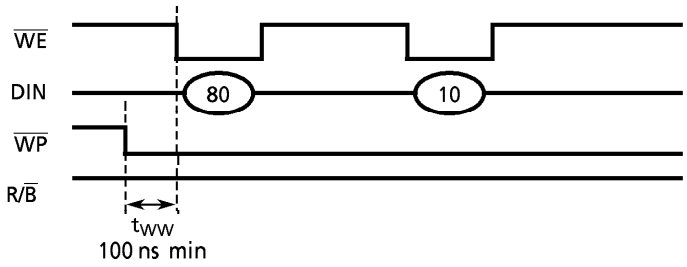
(9) Note regarding the $\overline{WP}$ signal

The Erase and Program operations are automatically reset when $\overline{WP}$ goes Low. The operations are enabled and disabled as follows:

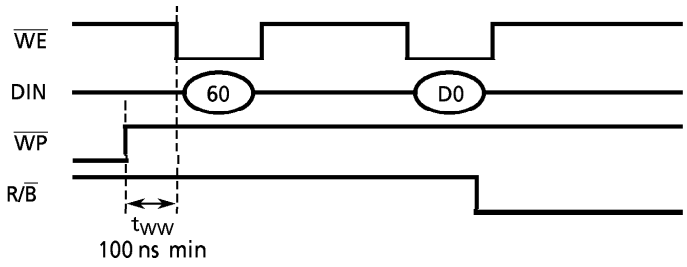
Enable Programming



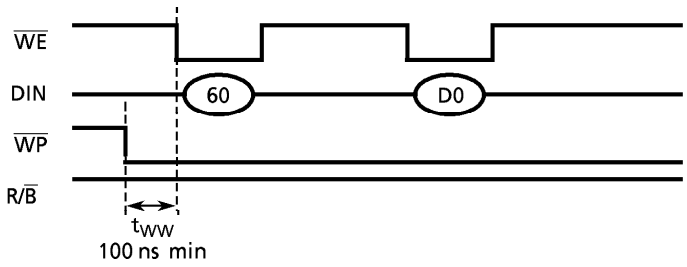
Disable Programming



Enable Erasing



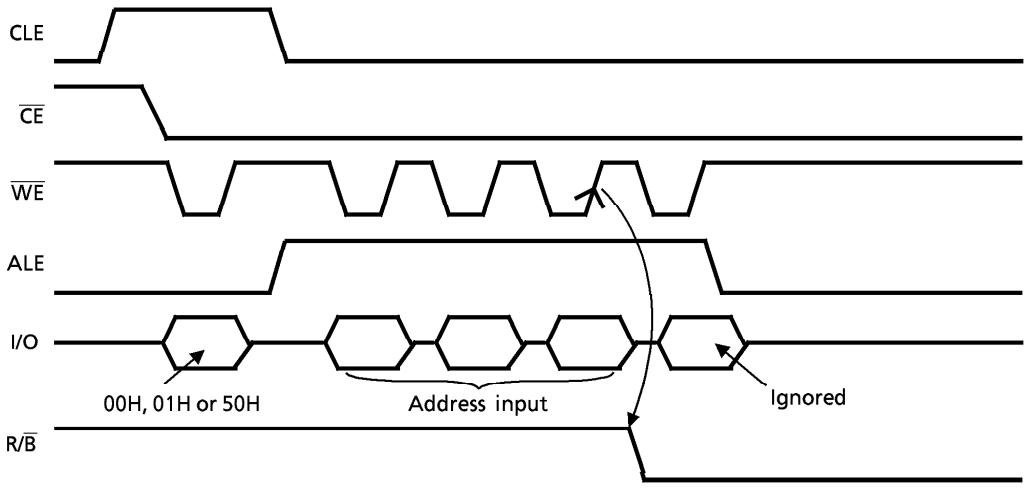
Disable Erasing



(10) When four address cycles are input

Although the device may read in a fourth address, it is ignored inside the chip.

Read operation



Internal read operation starts when $\overline{WE}$ goes High in the third cycle.

Figure 22.

Program operation

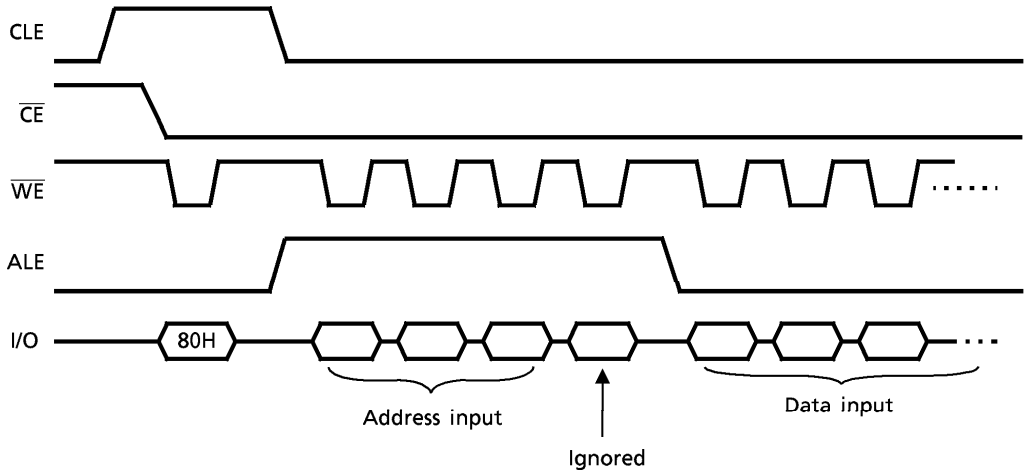


Figure 23.

(11) Several programming cycles on the same page (Partial Page Program)

A page can be divided into up to 10 segments. Each segment can be programmed individually as follows:

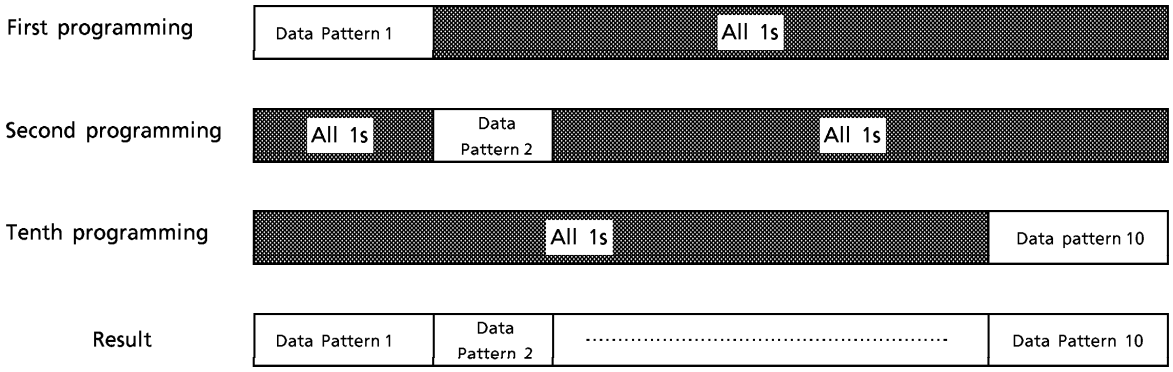


Figure 24.

Note: The input data for unprogrammed or previously programmed page segments must be 1 (i.e. the inputs for all page bytes outside the segment which is to be programmed should be set to all 1s).

(12) Note regarding the $\overline{RE}$ signal

The internal column address counter is incremented synchronously with the $\overline{RE}$ clock in Read mode. Therefore, once the device has been set to Read mode by a 00H, 01H or 50H command, the internal column address counter is incremented by the $\overline{RE}$ clock independently of the address input timing. If the $\overline{RE}$ clock input pulses start before the address input, and the pointer reaches the last column address, an internal read operation (array → register) will occur and the device will enter Busy state. (Refer to Figure 25.)

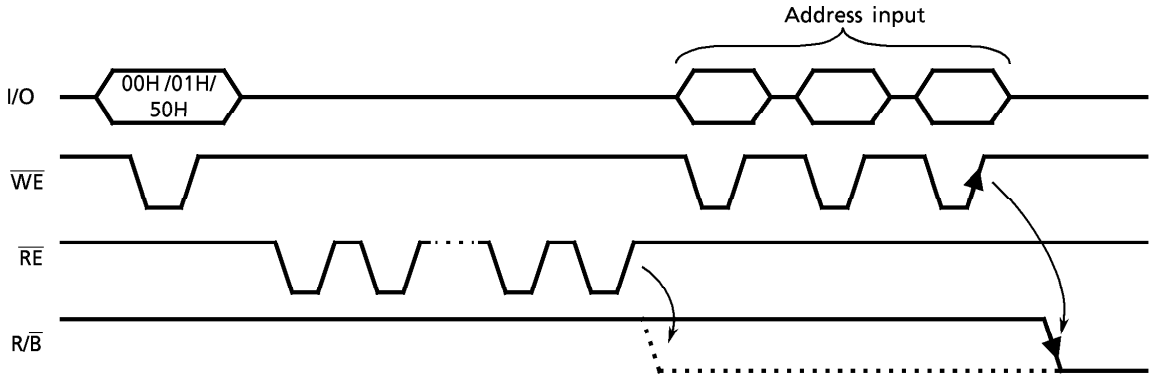


Figure 25.

Hence the $\overline{RE}$ clock input must start after the address input.

(13) Invalid blocks (bad blocks)

The device occasionally contains unusable blocks. Therefore, the following issues must be recognized:

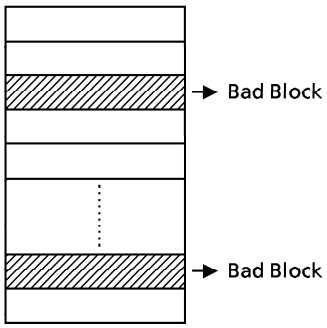


Figure 26.

Check to see whether the device has any bad blocks after installation of the device into the system. Do not try to access bad blocks. A bad block does not affect the performance of good blocks because it is isolated from the Bit line by the Select gate.

The number of valid blocks is as follows:

	MIN	TYP.	MAX	UNIT
Valid (Good) Blocks	1014	1020	1024	Block

Figure 28 shows the flow for bad block testing

(14) Failure phenomena for Program and Erase operations

The device may fail during a Program or Erase operation.

The following possible failure modes should be considered when implementing systems in which reliability is at a premium.

FAILURE MODE		DETECTION AND COUNTERMEASURE SEQUENCE
Block	Erase Failure	Status Read after Erase → Block Replacement
Page	Programming Failure	Status Read after Program → Block Replacement
Single Bit*	Programming Failure 1→0	(1) Block Verify after Program → Retry
		(2) ECC

* : (1) or (2)

- ECC : Error Correction Code → Hamming Code etc.
  Example: 1-bit correction & 2-bit detection
- Block Replacement

Program

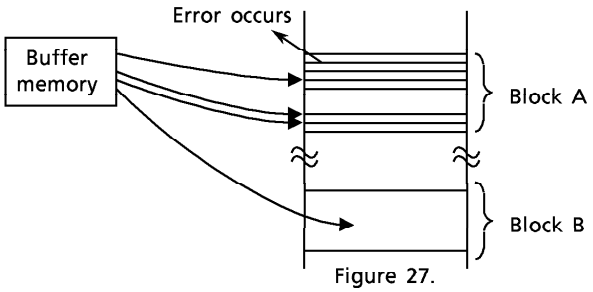


Figure 27.

When an error occurs in Block A, try to reprogram the data into another block (e.g. Block B) by loading it from an external buffer. Then, prevent further system accesses to Block A (by creating a bad block table or by using another appropriate scheme).

Erase

When an error occurs in an Erase operation, prevent future accesses to this bad block (again by creating a table within the system or by using another appropriate scheme).

BAD BLOCK TEST FLOW

C : Checkerboard pattern
$\overline{C}$: Inverted checkerboard pattern
Blank check : 1 Block Read (FFH)

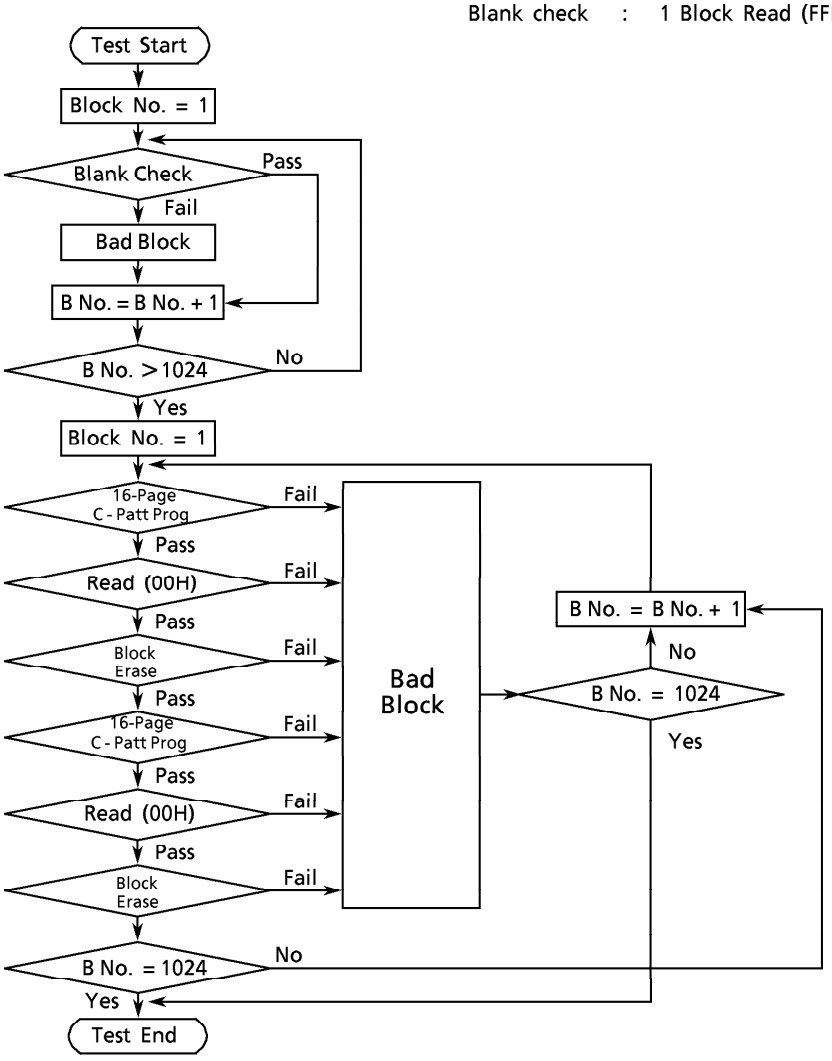


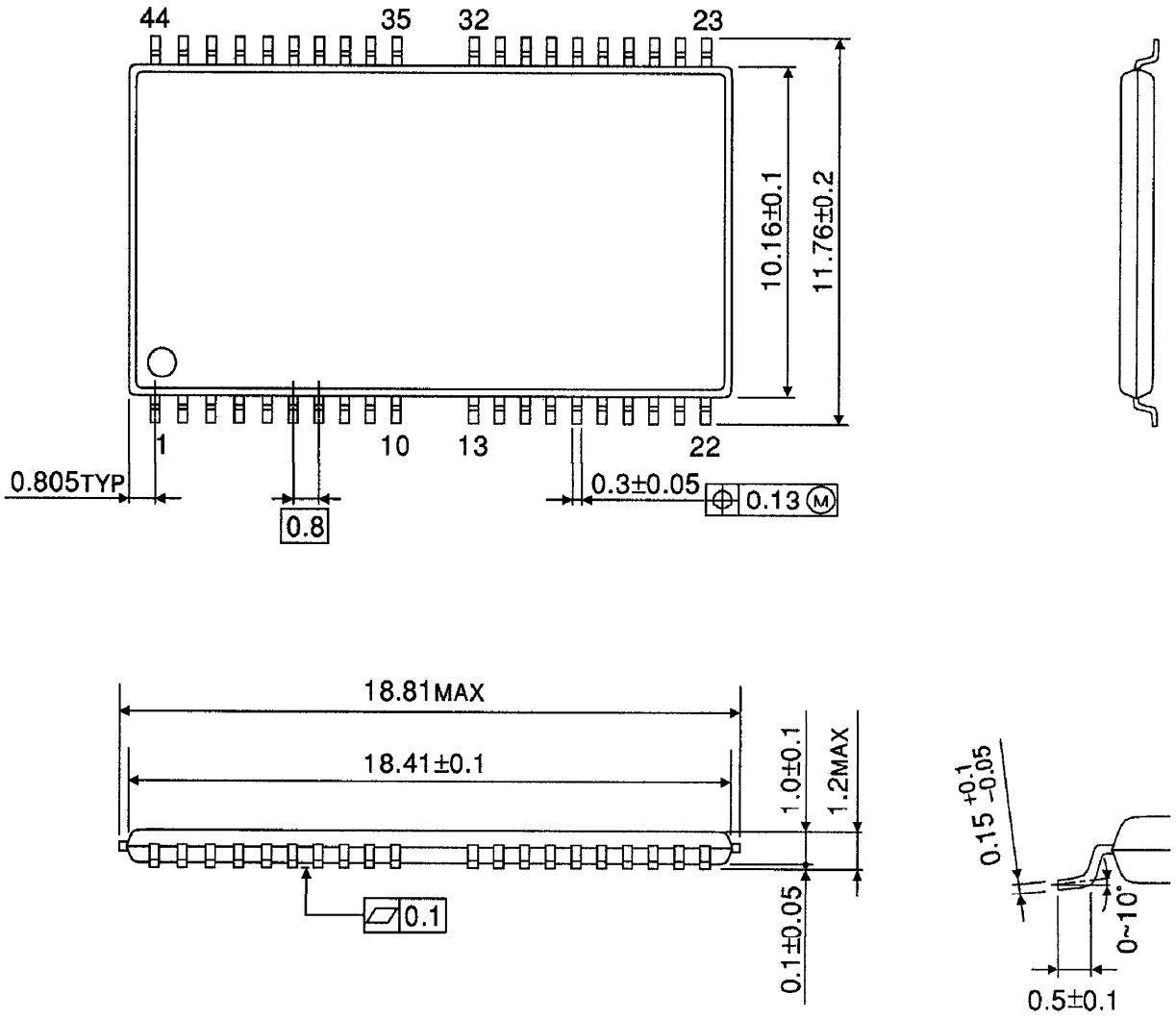
Figure 28.

PACKAGE DIMENSIONS

Plastic TSOP

TSOP Ⅱ 44/40-P-400-0.80B

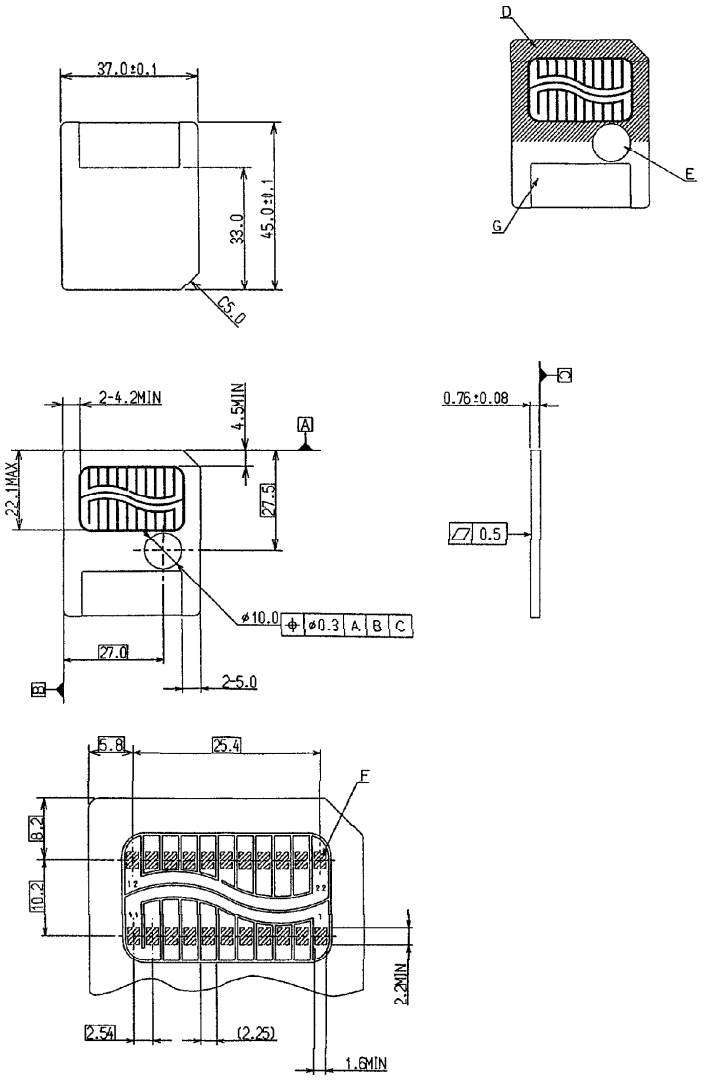
Unit: mm



PACKAGE DIMENSIONS

FDC-22A

Unit: mm



E : Write-protect area

F : The distance between the surface of D and all contact areas is less than 0.1 mm.

G: Index area